TPS1HA08-Q1 40V、8mΩ 单通道智能高侧开关

1 特性

- 具有 8mΩ R_{ON} (T_J = 25°C) 的单通道智能高侧开关
- 符合汽车类 应用的 16 通道 AFE：
  - 符合 AEC Q-100 标准
  - 器件温度等级 1：–40°C 至 +125°C 的环境工作温度范围
  - 可承受 40V 负载突降
- 提供功能安全
  - 提供文档以帮助创建功能安全系统设计
- 通过可选电流限制提高可靠性
  - 电流限制设置点为 20A 或 80A
  - 电流钳位或瞬时关断的过流响应
- 强大的集成输出保护：
  - 集成热保护
  - 接地短路和电池短路保护
  - 电池反向时自动启动
  - 发生失电和接地失效时自动关闭
  - 集成输出钳位对电感负载进行消磁
  - 可配置故障处理
- 可对模拟检测输出进行配置，以精确测量：
  - 负载电流
  - 电源电压
  - 器件温度
- 将 FLT 指示返回到 MCU
  - 开路负载和电池短路检测

2 应用

- 车身控制模块
- 白炽灯和 LED 照明
- 加热元件：
  - 座椅加热器
  - 火花塞
  - 油箱加热器
- 变速器控制单元
- 汽车空调
- 信息娱乐系统显示屏
- ADAS 模块

3 说明

器件是一款适用于 12V 汽车系统的单通道智能高侧开关。该器件集成了强大的保护和诊断 功能 以确保在短路等有害事件中提供输出端口保护。该器件通过可靠的电流限制来防止故障，其中电流限制可设置为 80A 和 20A（取决于器件型号），也可配置为通过立即关断开关或将输出电流调节为设置点来应对过流事件。高电流限制选项使其可用于需要大瞬态电流的负载，而低电流限制选项可为不需要高峰值电流的负载提供更好的保护。

还可提供高精度模拟电流检测，可在进行不同的负载分布时改进诊断。通过向系统 MCU 报告负载电流、设备温度和电源电压，该器件可实现预测性维护和负载诊断，从而延长系统寿命。

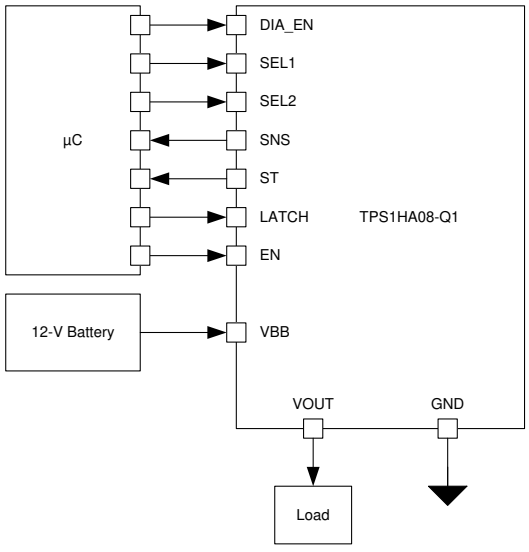
采用小型的 16 引脚 HTSSOP 封装，可减小 PCB 尺寸。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TPS1HA08-Q1	HTSSOP (16)	5.00mm x 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化原理图



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4 修订历史记录

Changes from Revision C (May 2019) to Revision D — **Page**

- 向*特性* 部分添加了提供功能安全的链接 ... 1

Changes from Revision B (January 2019) to Revision C — **Page**

- 已添加 向*特性* 和*说明* 部分添加了指向引用应用手册的链接 ... 1
- Removed the Product Preview note from Device Version B,D,E in the *Device Comparison Table* ... 3
- Updated the *Absolute Maximum Ratings* and *Electrical Characteristics* tables in the *Specifications* section ... 6
- Updated 图 7 ... 13
- 已添加 paragragh to the *Undervoltage Lockout (UVLO)* section ... 22
- Added app note link to 图 41 title ... 24

Changes from Revision A (December 2018) to Revision B — **Page**

- Deleted note from Device Version C in the *Device Comparison Table* ... 3

Changes from Original (September 2017) to Revision A — **Page**

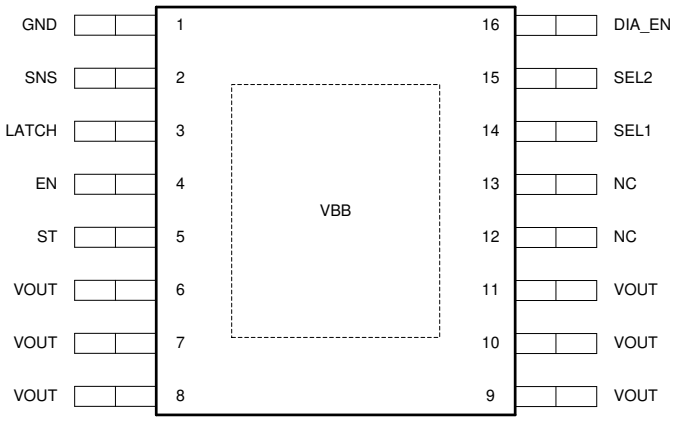
- 已更改 从“预告信息”更改为“生产数据” ... 1

5 Device Comparison Table

Device Version	Full Device Number	Current Limit (I_{CL})	Overcurrent Behavior	Watchdog Feature
A	TPS1HA08**A**-Q1	20 A	Disable Switch Immediately	Disabled
B	TPS1HA08**B**-Q1	80 A	Disable Switch Immediately	Disabled
C	TPS1HA08**C**-Q1	20 A	Clamp Current at I_{CL} until Thermal Shutdown	Disabled
D	TPS1HA08**D**-Q1	80 A	Clamp Current at I_{CL} until Thermal Shutdown	Disabled
E	TPS1HA08**E**-Q1	20 A	Disable Switch Immediately	Enabled

6 Pin Configuration and Functions

PWP Package
16-Pin HTSSOP
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	GND	—	Device ground
2	SNS	O	Sense output
3	LATCH	I	Sets fault handling behavior (latched or auto-retry)
4	EN	I	Switch control input, active high
5	$\overline{ST}$	O	Switch diagnostic feedback, active low
6, 7, 8, 9, 10, 11	VOUT	O	Switch output
12	NC	--	No Connect
13	NC	--	No Connect
14	SEL1	I	Diagnostics Select 1
15	SEL2	I	Diagnostics Select 2
16	DIA_EN	I	Diagnostic enable, active high
Exposed pad	VBB	I	Power supply input

6.1 Recommended Connections for Unused Pins

The device is designed to provide an enhanced set of diagnostic and protection features. However, if the system design only allows for a limited number of I/O connections, some pins may be considered as optional.

Table 1. Connections for Optional Pins

PIN NAME	CONNECTION IF NOT USED	IMPACT IF NOT USED
SNS	Ground through 1-kΩ resistor	Analog sense is not available.
LATCH	Float or ground through R_{PROT} resistor	With LATCH unused, the device will auto-retry after a fault. If latched behavior is desired it is possible to use one microcontroller output to control the latch function of several high-side channels.
$\overline{ST}$	Float	All faults are indicated by the analog SNS pin. The $\overline{ST}$ pin provides the additional benefits: • Provide fault indication when DIA_EN = 0 • Provide fault indication regardless of SELx pin conditions • Provide fault indication to a simple digital I/O (rather than ADC or comparator used with the SNS signal)
SEL1	Float or ground through R_{PROT} resistor	SEL1 selects between the V_{BB} and T_J sensing features. With SEL1 unused, only load diagnostics are available.
SEL2	Ground through R_{PROT} resistor	With SEL2 = 0 V, V_{BB} measurement diagnostics are not available.
DIA_EN	Float or ground through R_{PROT} resistor	With DIA_EN unused, analog sense, open-load and short-to-battery diagnostics are not available.

R_{PROT} is used to protect the pins from excess current flow during reverse battery conditions, for more information please see the section on *Reverse Battery* protection.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{BB}	Maximum continuous supply voltage			36	V
V_{LD}	Load dump voltage	ISO16750-2:2010(E)		40	V
V_{Rev}	Reverse battery voltage, V_{REV} ≤ 3 minutes		–18		V
V_{EN}	Enable pin voltage		–1	7	V
V_{LATCH}	LATCH pin voltage		–1	7	V
V_{ST}	Status pin voltage		–1	7(2)	V
V_{DIA_EN}	Diagnostic Enable pin voltage		–1	7	V
V_{SNS}	Sense pin voltage		–1	7	V
V_{SEL1}, V_{SEL2}	Select pin voltage		–1	7	V
I_{GND}	Reverse ground current	V_{BB} < 0 V		–50	mA
E_{TOFF}	Energy dissipation during turn-off	Single pulse, L_{OUT} = 5 mH, T_A = 125°C		95	mJ
		Repetitive pulse, 10 Hz, L_{OUT} = 5 mH, T_A = 125°C		56	mJ
T_J	Maximum junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) These pins are adjacent to pins that will handle high-voltages. In the event of a pin-to-pin short, there will not be device damage.

7.2 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002(1)	All pins except exposed pad and pins 6 to 11	±2000	V
			Exposed pad and pins 6 to 11	±4000	
		Charged-device model (CDM), per AEC Q100-011	All pins	±750	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{BB}	Nominal supply voltage		8	18	V
V_{BB}	Extended operating range (1)		3	28	V
V_{EN}	Enable voltage		–1	5.5	V
V_{LATCH}	LATCH voltage		–1	5.5	V
V_{DIA_EN}	Diagnostic enable voltage		–1	5.5	V
V_{SEL1}, V_{SEL2}	Select voltage		–1	5.5	V
V_{ST}	Status voltage		0	5.5	V
V_{SNS}	Sense voltage		–1	$V_{SNSclamp}$	V
I_{MAX}	Continuous load current	T_A = 70°C	0	10	A

(1) Device will function within extended operating range, however some parametric values might not apply

7.4 Thermal Information

THERMAL METRIC(1)(2)		TPS1HA08-Q1 PWP (HTSSOP) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	32.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	30.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	9.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	2.6	°C/W
ψ_{JB}	Junction-to-board characterization parameter	9.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	1.0	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.
(2) The thermal parameters are based on a 4-layer PCB according to the JESD51-5 and JESD51-7 standards.

7.5 Electrical Characteristics

V_{BB} = 8 V to 18 V, T_J = –40°C to 150°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT VOLTAGE AND CURRENT						
V_{Clamp}	V_{DS} clamp voltage		40		58	V
V_{UVLOF}	V_{BB} undervoltage lockout falling			2.5	3	V
V_{UVLOR}	V_{BB} undervoltage lockout rising			2.5	3	V
I_{SB}	Standby current (includes MOSFET leakage)	V_{BB} = 13.5 V, T_J = 25°C V_{EN} = V_{DIA_EN} = 0 V, V_{OUT} = 0 V			0.5	µA
		V_{BB} = 13.5 V, T_J = 85°C V_{EN} = V_{DIA_EN} = 0 V, V_{OUT} = 0 V			0.5	µA
		V_{BB} = 13.5 V, T_J = 125°C, V_{EN} = V_{DIA_EN} = 0 V, V_{OUT} = 0 V			3	µA
$I_{OUT(standby)}$	Output leakage current	V_{BB} = 13.5 V, T_J = 25°C V_{EN} = V_{DIA_EN} = 0 V, V_{OUT} = 0 V		0.01	0.5	µA
		V_{BB} = 13.5 V, T_J = 125°C V_{EN} = V_{DIA_EN} = 0 V, V_{OUT} = 0 V			3	µA
I_{DIA}	Current consumption in diagnostic mode	V_{BB} = 13.5 V, I_{SNS} = 0 mA V_{EN} = 0 V, V_{DIA_EN} = 5 V, V_{OUT} = 0V		3	6	mA
I_Q	Quiescent current	V_{BB} = 13.5 V V_{EN} = V_{DIA_EN} = 5 V, I_{OUT} = 0 A, V_{SELX} = 0 V		3	6	mA
t_{STBY}	Standby mode delay time	V_{EN} = V_{DIA_EN} = 0 V to Standby		20		ms
R_{ON} CHARACTERISTICS						
R_{ON}	On-resistance Includes MOSFET and package	T_J = 25°C, 6 V ≤ V_{BB} ≤ 28 V		9		mΩ
		T_J = 150°C, 6 V ≤ V_{BB} ≤ 28 V			20	mΩ
		T_J = 25°C, 3 V ≤ V_{BB} ≤ 6 V			15	mΩ
$R_{ON(REV)}$	On-resistance during reverse polarity	T_J = 25°C, -18 V ≤ V_{BB} ≤ -8 V		9		mΩ
		T_J = 105°C, -18 V ≤ V_{BB} ≤ -8 V			20	mΩ
CURRENT SENSE CHARACTERISTICS						
K_{SNS}	Current sense ratio I_{OUT} / I_{SNS}			4600		

Electrical Characteristics (continued)

V_{BB} = 8 V to 18 V, T_J = –40°C to 150°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{SNSI}	Current sense current and current sense accuracy	V_{EN} = V_{DIA_EN} = 5 V, V_{SEL1} = V_{SEL2} = 0 V	I_{OUT} = 20 A		4.35		mA
				–5		5	%
			I_{OUT} = 8 A		1.74		mA
				–5		5	%
			I_{OUT} = 3 A		0.65		mA
				–5		5	%
			I_{OUT} = 1 A		0.217		mA
				–5		5	%
			I_{OUT} = 300 mA		0.065		mA
				–12		12	%
			I_{OUT} = 100 mA		0.022		mA
				–42		42	%
T_J SENSE CHARACTERISTICS							
I_{SNST}	Temperature sense current	V_{DIA_EN} = 5 V, V_{SEL1} = 5 V, V_{SEL2} = 0 V	T_J = –40°C		0.12		mA
			T_J = 25°C		0.85		mA
			T_J = 85°C		1.52		mA
			T_J = 150°C		2.25		mA
dI_{SNST}/dT	Coefficient				0.0112		mA/°C
V_{BB} SENSE CHARACTERISTICS							
I_{SNSV}	Voltage sense current	V_{DIA_EN} = 5 V, V_{SEL1} = 5 V, V_{SEL2} = 5 V	V_{BB} = 3 V		0.26		mA
			V_{BB} = 8 V		0.69		mA
			V_{BB} = 13.5 V		1.17		mA
			V_{BB} = 18 V		1.56		mA
			V_{BB} = 28 V		2.43		mA
dI_{SNSV}/dV	Coefficient				0.0867		mA/V
SNS CHARACTERISTICS							
I_{SNSFH}	I_{SNS} fault high level	V_{DIA_EN} = 5 V, V_{SEL1} = 0 V, V_{SEL2} = 0		6	6.9	7.6	mA
$I_{SNSleak}$	I_{SNS} leakage	V_{DIA_EN} = 0 V		0		1	µA
$V_{SNSclamp}$	V_{SNS} clamp				5.9		V
CURRENT LIMIT CHARACTERISTICS							
I_{CL}	Current Limit	Device Version B/D	T_J = –40°C	75.5	88.8	102.1	A
			T_J = 25°C	68	80	92	
			T_J = 150°C	51	60	69	
		Device Version A/C/E	T_J = –40°C	16	22.2	27.8	A
			T_J = 25°C	14.4	20	25	
			T_J = 150°C	10.8	15	18.8	
$\overline{ST}$ PIN CHARACTERISTICS							
V_{OL}	Open-load detection voltage	V_{EN} = 0 V, V_{DIA_EN} = 5 V		2	2.5	4	V
t_{OL1}	OL and STB indication time - switch disabled	From falling edge of EN V_{EN}= 5 V to 0 V, V_{DIA_EN} = 5 V, V_{SELx} = 00 I_{OUT} = 0 mA, V_{OUT} = 4 V		300	500	700	µs
t_{OL2}	OL and STB indication time - switch disabled	From rising edge of DIA_EN V_{EN} = 0 V, V_{DIA_EN} = 0 V to 5 V, V_{SELx} = 00 I_{OUT} = 0 mA, V_{OUT} = 4 V				50	µs
t_{OL3}	OL and STB indication time - switch disabled	From rising edge of VOUT V_{EN} = 0 V, V_{DIA_EN} = 5 V, V_{SELx} = 00 I_{OUT} = 0 mA, V_{OUT} = 0 V to 4 V				50	µs
T_{ABS}	Thermal shutdown			160			°C
T_{HYS}	Thermal shutdown hysteresis				20		°C
t_{RETRY}	Retry time	Minimum time from fault shutdown to switch re-enable (for thermal shutdown, current limit, and energy limit)		1	2	3	ms
t_{WD}	Watchdog timer	Device version E		350	400	450	ms

Electrical Characteristics (continued)

V_{BB} = 8 V to 18 V, T_J = –40°C to 150°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
EN PIN CHARACTERISTICS (1)						
$V_{IL, EN}$	Input voltage low level				0.8	V
$V_{IH, EN}$	Input voltage high level	No GND network Diode	2			V
$V_{IHYS, EN}$	Input voltage hysteresis	No GND network Diode		250		mV
$I_{IL, EN}$	Input current low level	V_{EN} = 0.8 V		0.8		µA
$I_{IH, EN}$	Input current high level	V_{EN} = 2.0 V		2		µA
R_{EN}	Internal pulldown resistor			1		MΩ
DIA_EN PIN CHARACTERISTICS (1)						
V_{IL, DIA_EN}	Input voltage low level	No GND network Diode			0.8	V
V_{IH, DIA_EN}	Input voltage high level	No GND network Diode	2			V
V_{IHYS, DIA_EN}	Input voltage hysteresis			250		mV
I_{IL, DIA_EN}	Input current low level	V_{DIA_EN} = 0.8 V		0.8		µA
I_{IH, DIA_EN}	Input current high level	V_{DIA_EN} = 2.0 V		2		µA
R_{DIA_EN}	Internal pulldown resistor			1		MΩ
SEL1 AND SEL2 PIN CHARACTERISTICS (1)						
$V_{IL, SELx}$	Input voltage low level	No GND network Diode			0.8	V
$V_{IH, SELx}$	Input voltage high level		2			V
$V_{IHYS, SELx}$	Input voltage hysteresis			250		mV
$I_{IL, SELx}$	Input current low level	V_{SELx} = 0.8 V		0.8		µA
$I_{IH, SELx}$	Input current high level	V_{SELx} = 2.0 V		2		µA
R_{SELx}	Internal pulldown resistor			1		MΩ
LATCH PIN CHARACTERISTICS (1)						
$V_{IL, LATCH}$	Input voltage low level	No GND network Diode			0.8	V
$V_{IH, LATCH}$	Input voltage high level	No GND network Diode	2			V
$V_{IHYS, LATCH}$	Input voltage hysteresis			250		mV
$I_{IL, LATCH}$	Input current low level	V_{LATCH} = 0.8 V		0.8		µA
$I_{IH, LATCH}$	Input current high level	V_{LATCH} = 2.0 V		2		µA
R_{LATCH}	Internal pulldown resistor			1		MΩ
ST PIN CHARACTERISTICS (1)						
$V_{OL, ST}$	Output voltage low level	I_{ST} = 1 mA			0.4	V
I_{STleak}	Leakage current	V_{ST} = 5 V			2	µA

(1) V_{BB} = 3 to 28 V

7.6 Switching Characteristics

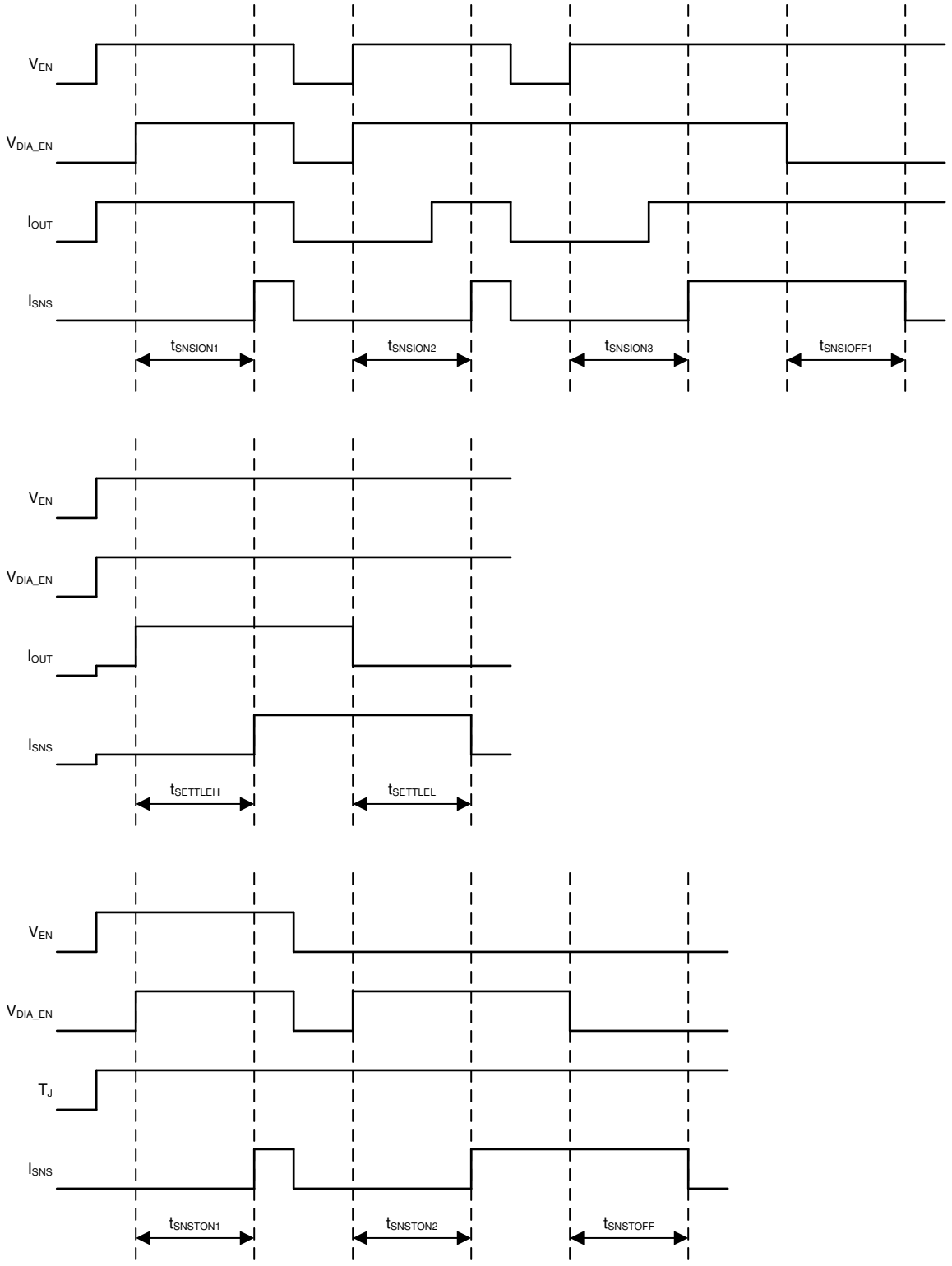
V_{BB} = 13.5 V, T_J = –40°C to 150°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{DR}	Turn-on delay time	V_{BB} = 13.5 V, R_L = 2.6 Ω	20	70	100	µs
t_{DF}	Turn-off delay time	V_{BB} = 13.5 V, R_L = 2.6 Ω	20	50	100	µs
SR_R	VOUT rising slew rate	V_{BB} = 13.5 V, 20% to 80% of V_{OUT}, R_L = 2.6 Ω	0.1	0.35	0.7	V/µs
SR_F	VOUT falling slew rate	V_{BB} = 13.5 V, 80% to 20% of V_{OUT}, R_L = 2.6 Ω	0.1	0.5	0.7	V/µs
t_{ON}	Turn-on time	V_{BB} = 13.5 V, R_L = 2.6 Ω	39	80	145	µs
t_{OFF}	Turn-off time	V_{BB} = 13.5 V, R_L = 2.6 Ω	39	75	145	µs
t_{ON} - t_{OFF}	Turn-on and off matching	200-µs enable pulse	–50	0	50	µs
E_{ON}	Switching energy losses during turn-on	V_{BB} = 13.5 V, R_L = 2.6 Ω		0.4		mJ
E_{OFF}	Switching energy losses during turn-off	V_{BB} = 13.5 V, R_L = 2.6 Ω		0.4		mJ

7.7 SNS Timing Characteristics

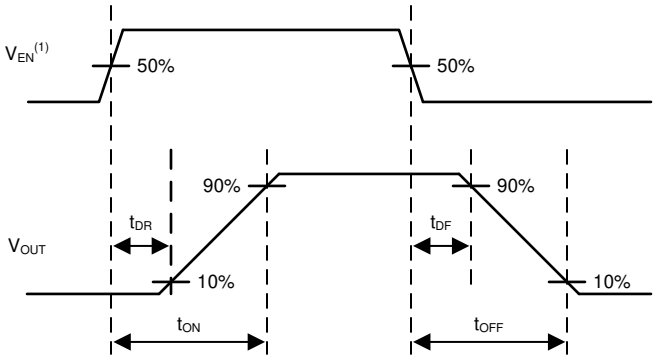
V_{BB} = 8 to 18 V, T_J = –40°C to 150°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SNS TIMING - CURRENT SENSE						
$t_{SNSION1}$	Settling time from rising edge of DIA_EN	V_{EN} = 5 V, V_{DIA_EN} = 0 V to 5 V R_{SNS} = 1 kΩ, R_L = 2.6 Ω			40	µs
$t_{SNSION2}$	Settling time from rising edge of EN	V_{EN} = V_{DIA_EN} = 0 V to 5 V R_{SNS} = 1 kΩ, R_L = 2.6 Ω			180	µs
$t_{SNSION3}$	Settling time from rising edge of EN	V_{EN} = 0 V to 5 V, V_{DIA_EN} = 5 V R_{SNS} = 1 kΩ, R_L = 2.6 Ω			180	µs
$t_{SNSIOFF1}$	Settling time from falling edge of DIA_EN	V_{EN} = 5 V, V_{DIA_EN} = 5 V to 0 V R_{SNS} = 1 kΩ, R_L = 2.6 Ω			20	µs
$t_{SETTLEH}$	Settling time from rising edge of load step	V_{EN} = 5 V, V_{DIA_EN} = 5 V R_{SNS} = 1 kΩ, I_{OUT} = 1 A to 5 A			20	µs
$t_{SETTLEL}$	Settling time from falling edge of load step	V_{EN} = 5 V, V_{DIA_EN} = 5 V R_{SNS} = 1 kΩ, I_{OUT} = 5 A to 1 A			20	µs
SNS TIMING - TEMPERATURE SENSE						
$t_{SNSTON1}$	Settling time from rising edge of DIA_EN	V_{EN} = 5 V, V_{DIA_EN} = 0 V to 5 V R_{SNS} = 1 kΩ			40	µs
$t_{SNSTON2}$	Settling time from rising edge of DIA_EN	V_{EN} = 0 V, $_{VDIA\_EN}$ = 0 V to 5 V R_{SNS} = 1 kΩ			70	µs
$t_{SNSTOFF}$	Settling time from falling edge of DIA_EN	V_{EN} = X, V_{DIA_EN} = 5 V to 0 V R_{SNS} = 1 kΩ			20	µs
SNS TIMING - VOLTAGE SENSE						
$t_{SNSVON1}$	Settling time from rising edge of DIA_EN	V_{EN} = 5 V, V_{DIA_EN} = 0 V to 5 V R_{SNS} = 1 kΩ			40	µs
$t_{SNSVON2}$	Settling time from rising edge of DIA_EN	V_{EN} = 0 V, V_{DIA_EN} = 0 V to 5 V R_{SNS} = 1 kΩ			70	µs
$t_{SNSVOFF}$	Settling time from falling edge of DIA_EN	V_{EN} = X, V_{DIA_EN} = 5 V to 0 V R_{SNS} = 1 kΩ			20	µs
SNS TIMING - MULTIPLEXER						
t_{MUX}	Settling time from temperature sense to current sense	V_{EN}= X, V_{DIA_EN} = 5 V V_{SEL1} = 5 V to 0 V, V_{SEL2} = 0 V R_{SNS} = 1 kΩ, R_L = 2.6 Ω			60	µs
	Settling time from temperature sense to voltage sense	V_{EN} = X, V_{DIA_EN} = 5 V V_{SEL1} = 5 V, V_{SEL2} = 0 V to 5 V R_{SNS} = 1 kΩ			60	µs
	Settling time from voltage sense to temperature sense	V_{EN} = X, V_{DIA_EN} = 5 V V_{SEL1} = 5 V, V_{SEL2} = 5 V to 0 V R_{SNS} = 1 kΩ			60	µs
	Settling time from voltage sense to current sense	V_{EN} = X, V_{DIA_EN} = 5 V V_{SEL1} = V_{SEL2} = 5 V to 0 V, R_{SNS} = 1 kΩ, R_L = 2.6 Ω			60	µs
	Settling time from current sense to temperature sense	V_{EN} = X, V_{DIA_EN} = 5 V V_{SEL1} = 0 V to 5 V, V_{SEL2} = 0 V R_{SNS} = 1 kΩ, R_L = 2.6 Ω			60	µs
	Settling time from current sense to voltage sense	V_{EN} = X, V_{DIA_EN} = 5 V V_{SEL1} = V_{SEL2} = 0 V to 5 V R_{SNS} = 1 kΩ, R_L = 2.6 Ω			60	µs



NOTES: Rise and fall times of control signals are 100 ns. Control signals include: EN, DIA_EN, SEL1, SEL2.
SEL1 and SEL2 must be set to the appropriate values.
The temperature sense timing diagram can also be used to depict the voltage sense timings.

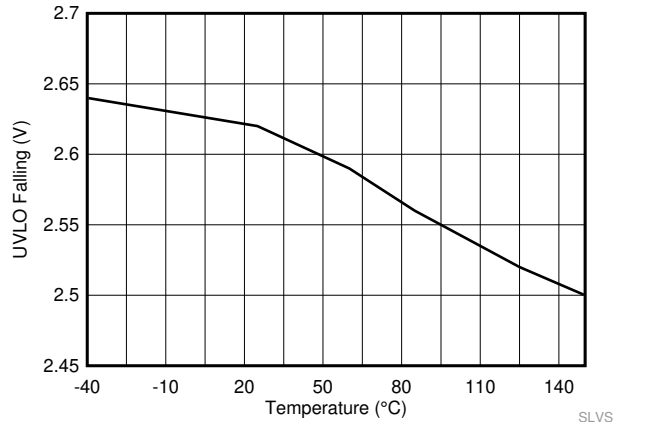
图 1. SNS Timing Characteristics Definitions



Rise and fall time of V_{EN} is 100 ns.

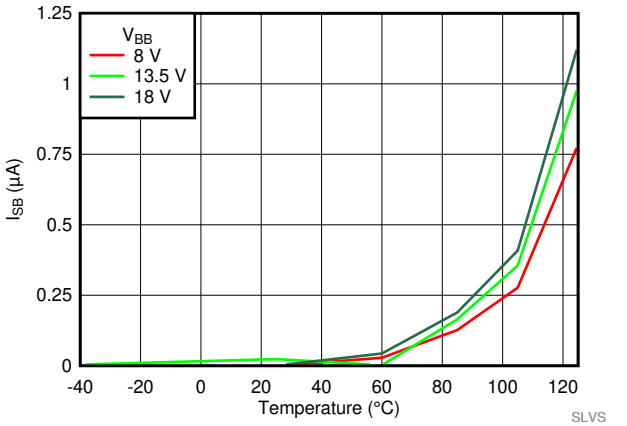
图 2. Switching Characteristics Definitions

7.8 Typical Characteristics



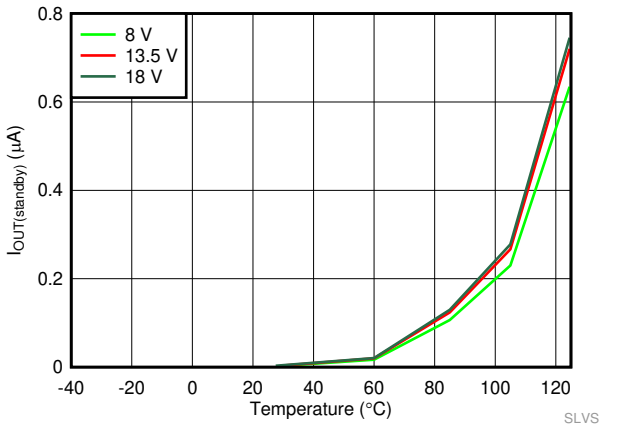
V_{BB} = 13.5 V to 0 V　R_{OUT} = 1 kΩ　V_{DIAG_EN} = 0 V
V_{EN} = 5 V

图 3. Falling Undervoltage Lockout (V_{UVLOF}) vs Temperature



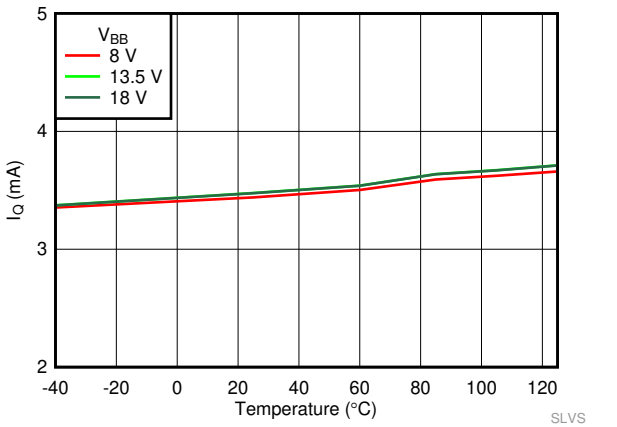
V_{OUT} = 0 V　V_{EN} = 0 V　V_{DIAG_EN} = 0 V

图 4. Standby Current (I_{SB}) vs Temperature



V_{OUT} = 0 V　V_{EN} = 0 V　V_{DIAG_EN} = 0 V

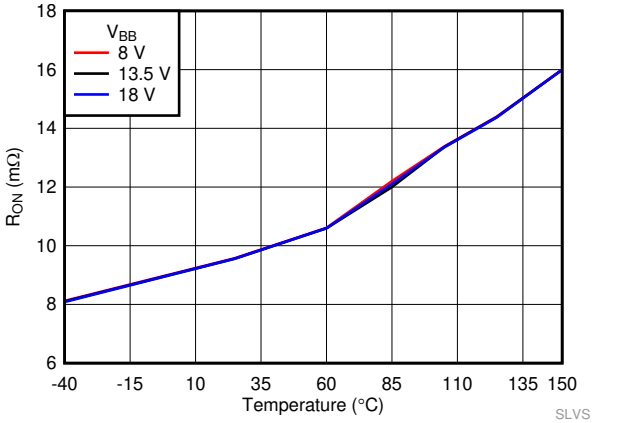
图 5. Output Leakage Current ($I_{OUT(standby)}$) vs Temperature



I_{OUT} = 0 A　V_{EN} = 5 V　V_{DIAG_EN} = 5 V
R_{SNS} = 1 kΩ　V_{SEL1} = V_{SEL2} = 0 V

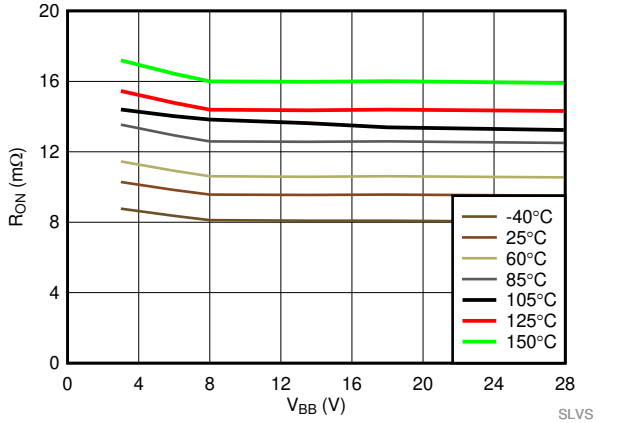
图 6. Quiescent Current (I_Q) vs Temperature

Typical Characteristics (接下页)



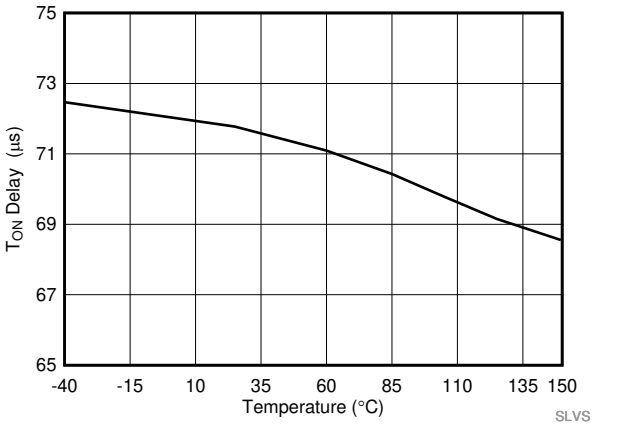
I_{OUT} = 200 mA V_{EN} = 5 V V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ

图 7. On Resistance (R_{ON}) vs Temperature



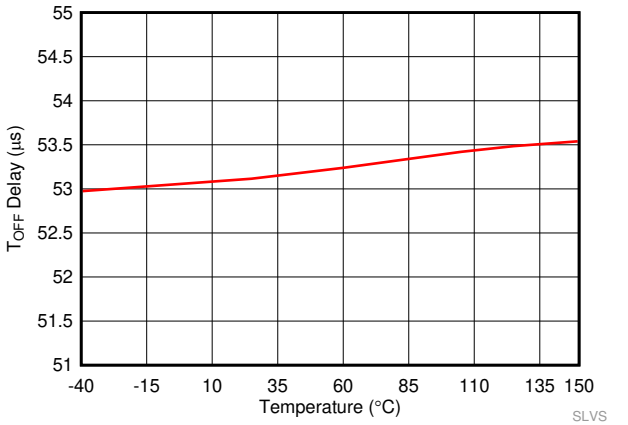
I_{OUT} = 200 mA V_{EN} = 5 V V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ V_{BB} = 13.5 V

图 8. On Resistance (R_{ON}) vs V_{BB}



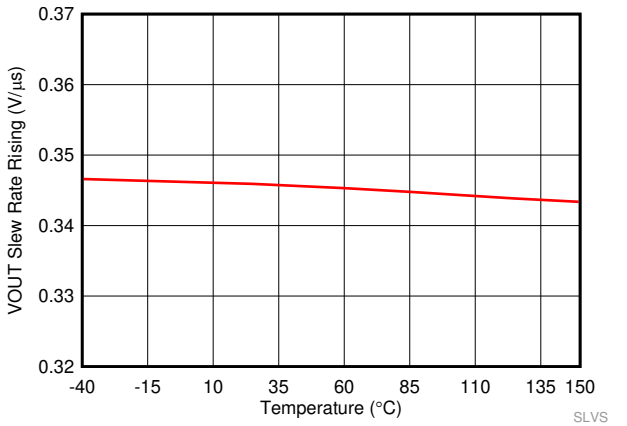
R_{OUT} = 2.6 Ω V_{EN} = 0 V to 5 V V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ V_{BB} = 13.5 V

图 9. Turn-on Delay Time (t_{DR}) vs Temperature



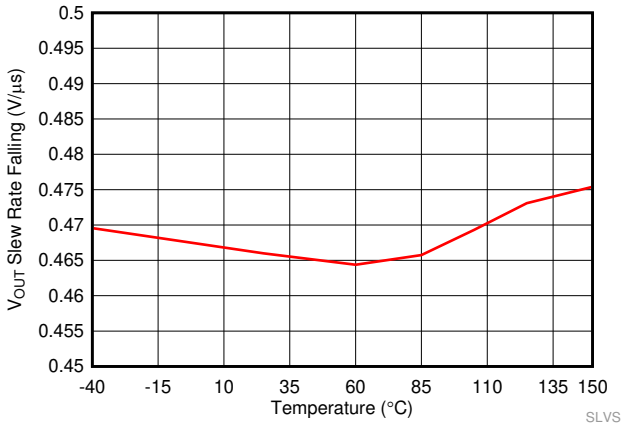
R_{OUT} = 2.6 Ω V_{EN} = 5 V to 0 V V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ V_{BB} = 13.5 V

图 10. Turn-off Delay Time (t_{DF}) vs Temperature



R_{OUT} = 2.6 Ω V_{EN} = 0 V to 5 V V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ V_{BB} = 13.5 V

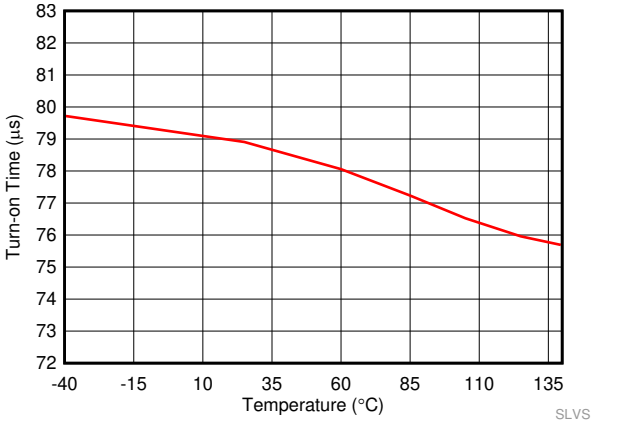
图 11. V_{OUT} Slew Rate Rising (SR_R) vs Temperature



R_{OUT} = 2.6 Ω V_{EN} = 5 V to 0 V V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ V_{BB} = 13.5 V

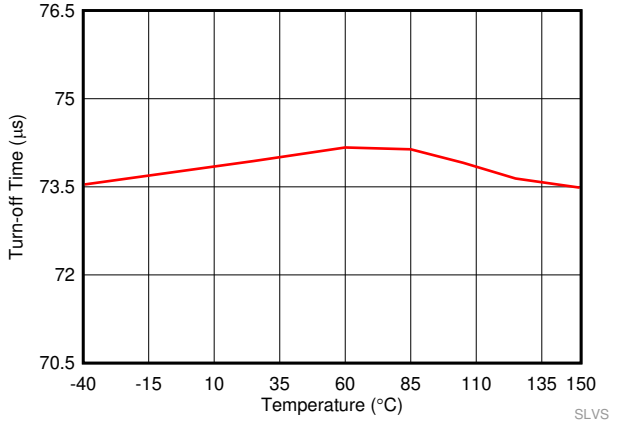
图 12. V_{OUT} Slew Rate Falling (SR_F) vs Temperature

Typical Characteristics (接下页)



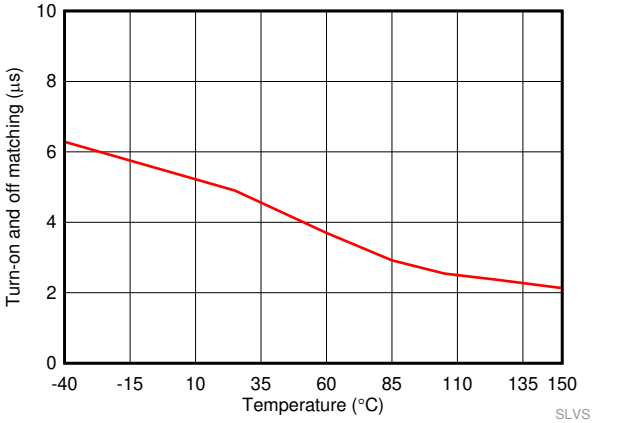
R_{OUT} = 2.6 Ω　V_{EN} = 0 V to 5 V　V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ　V_{BB} = 13.5 V

图 13. Turn-on Time (t_{ON}) vs Temperature



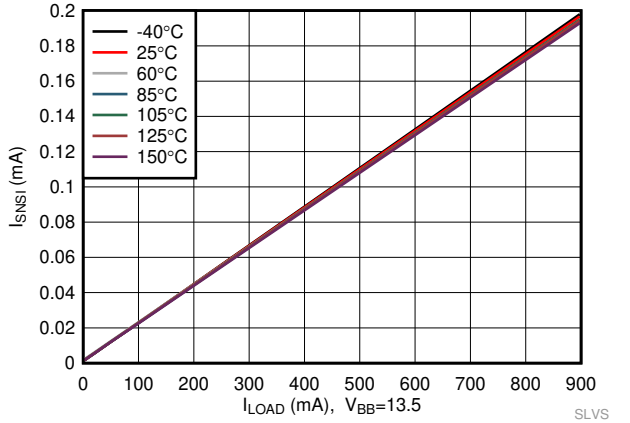
R_{OUT} = 2.6 Ω　V_{EN} = 5 V to 0 V　V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ　V_{BB} = 13.5 V

图 14. Turn-off Time (t_{OFF}) vs Temperature



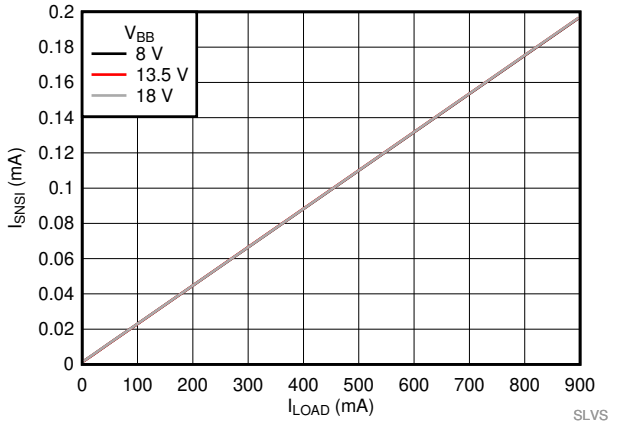
R_{OUT} = 2.6 Ω　V_{EN} = 0 V to 5 V and 5 V to 0 V　V_{DIAG_EN} = 0 V
R_{SNS} = 1 kΩ　V_{BB} = 13.5 V

图 15. Turn-on and Turn-off Matching (t_{ON} - t_{OFF}) vs Temperature



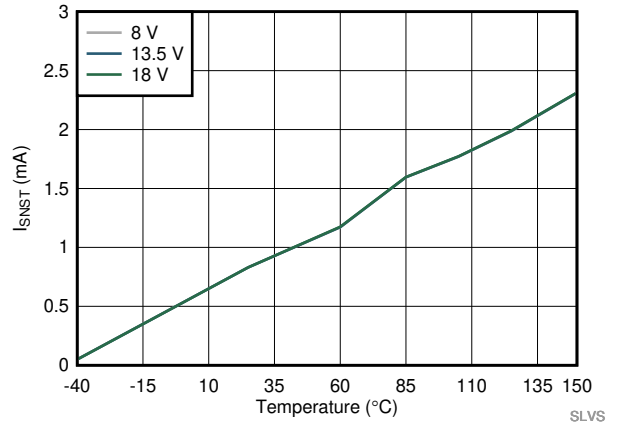
V_{SEL1} = V_{SEL2} = 0 V　V_{EN} = 5 V　V_{DIAG_EN} = 5 V
R_{SNS} = 1 kΩ　V_{BB} = 13.5 V

图 16. Current Sense Output Current (I_{SNSI}) vs Load Current (I_{OUT}) across Temperature



V_{SEL1} = V_{SEL2} = 0 V　V_{EN} = 5 V　V_{DIAG_EN} = 5 V
R_{SNS} = 1 kΩ　T_A = 25°C

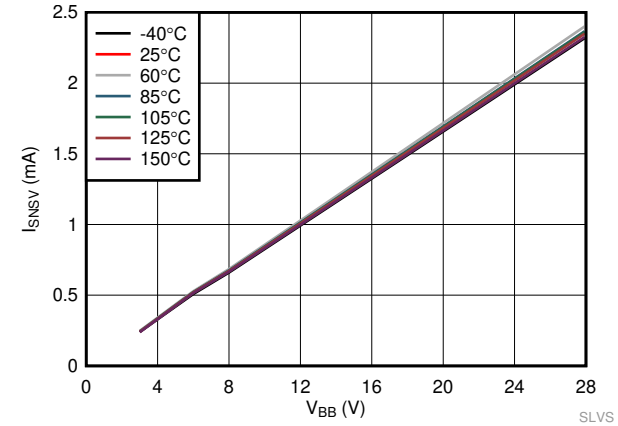
图 17. Current Sense Output Current (I_{SNSI}) vs Load Current (I_{OUT}) across V_{BB}



V_{SEL1} = 5 V　V_{SEL2} = 0 V　V_{DIAG_EN} = 5 V
R_{SNS} = 1 kΩ　V_{EN} = 0 V

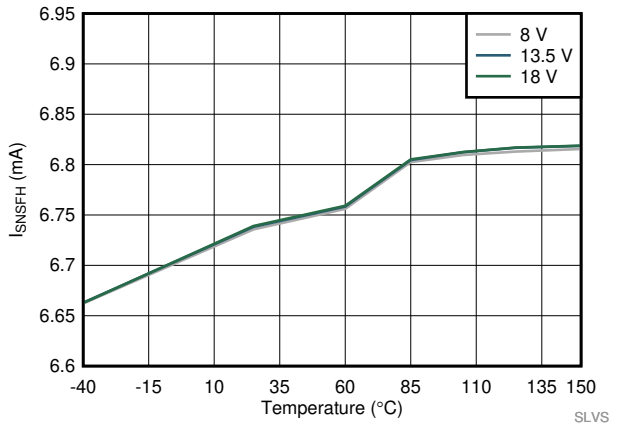
图 18. Temperature Sense Output Current (I_{SNST}) vs Temperature

Typical Characteristics (接下页)



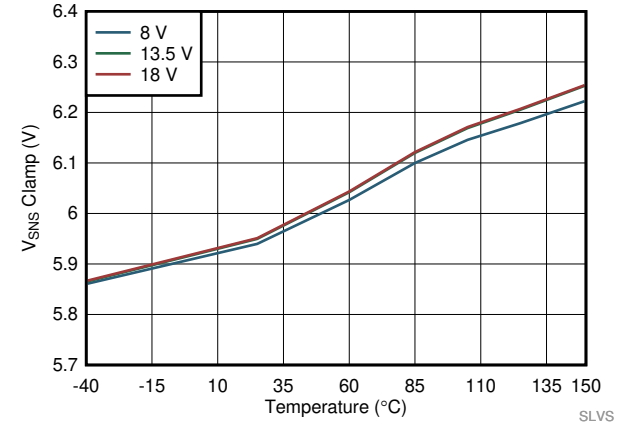
V_{SEL1} = V_{SEL2} = 5 V　　V_{EN} = 0 V　　V_{DIAG_EN} = 5 V
R_{SNS} = 1 kΩ　　I_{OUT} = 0 A

图 19. Voltage Sense Output Current (I_{SNSV}) vs V_{BB}



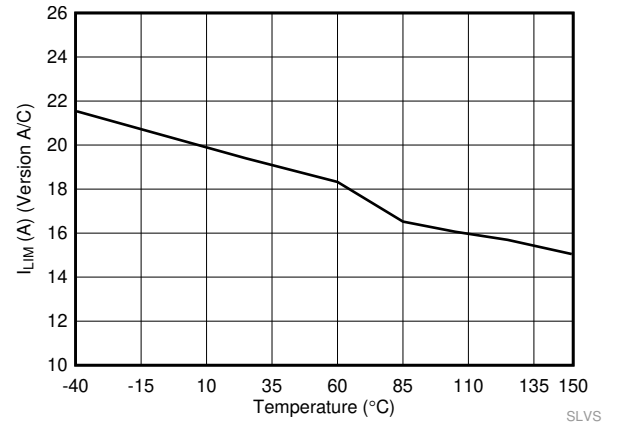
V_{SEL1} = V_{SEL2} = 0 V　　V_{EN} = 0 V　　V_{DIAG_EN} = 5 V
R_{SNS} = 500 Ω　　V_{OUT} Floating

图 20. Fault High Output Current (I_{SNSFH}) vs Temperature



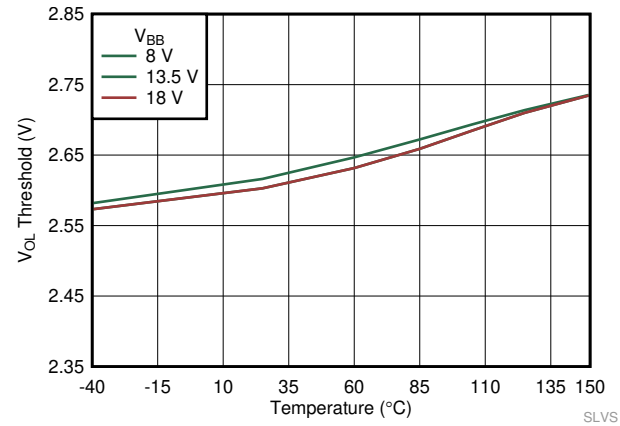
V_{SEL1} = V_{SEL2} = 0 V　　V_{EN} = 5 V　　V_{DIAG_EN} = 5 V
R_{SNS} = 10 kΩ　　I_{OUT} = 4 A

图 21. Sense Pin Clamp Voltage ($V_{SNSCLAMP}$) vs Temperature



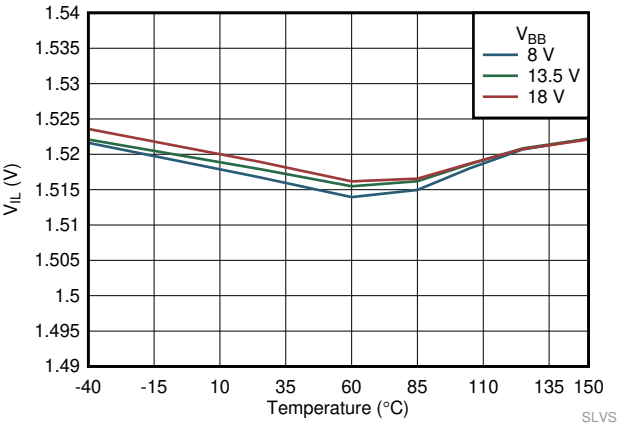
V_{BB} = 13.5 V　　V_{OUT} = 0 V　　V_{DIAG_EN} = 0 V
Device Version C　　V_{EN} = 5 V　　V_{LATCH} = 5 V

图 22. Current Limit (I_{CL}) vs Temperature



V_{EN} = 0 V　　V_{OUT} = 0 V to 5 V　　I_{OUT} = 0 A
V_{DIAG_EN}= 5 V　　V_{SEL1} = V_{SEL2} = 0 V

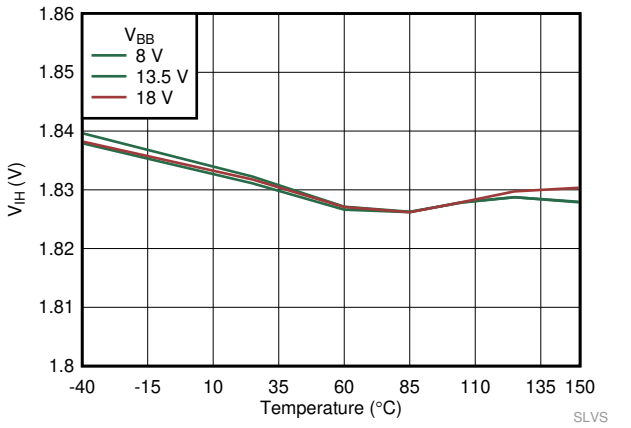
图 23. Open Load Detection Voltage (V_{OL}) vs Temperature



V_{EN} = 3.3 V to 0 V　　V_{OUT} = 0 V　　V_{DIAG_EN} = 0 V
R_{OUT} = 1 kΩ

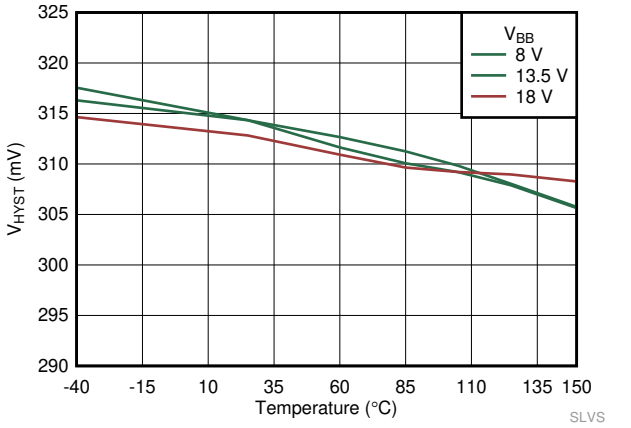
图 24. V_{IL} vs Temperature

Typical Characteristics (接下页)



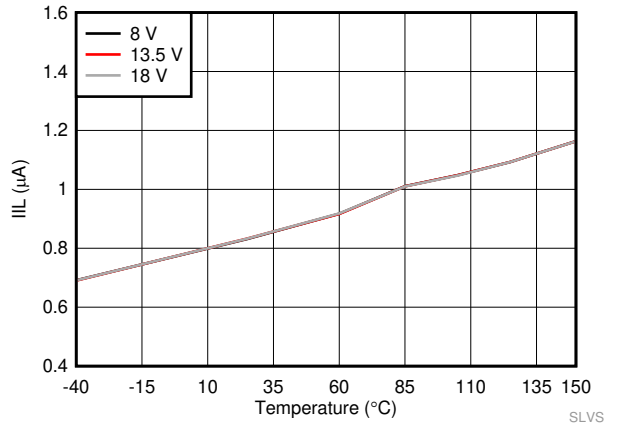
V_{EN} = 0 V to 3.3 V V_{OUT} = 0 V V_{DIAG_EN} = 0 V
R_{OUT} = 1 kΩ

图 25. V_{IH} vs Temperature



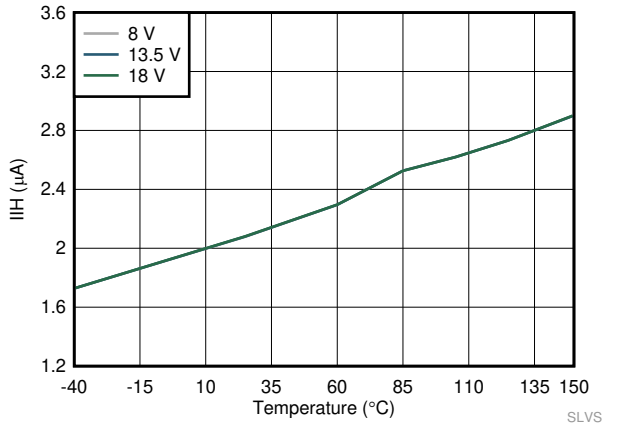
V_{EN} = 0 V to 3.3 V and 3.3 V to 0 V V_{OUT} = 0 V V_{DIAG_EN} = 0 V
R_{OUT} = 1 kΩ

图 26. V_{IHYS} vs Temperature



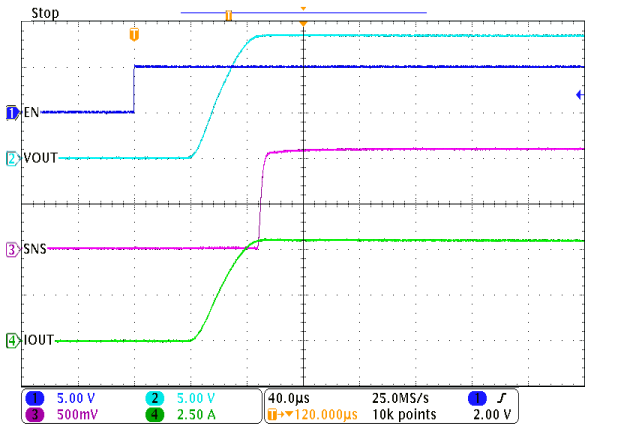
V_{EN} = 0.8 V V_{OUT} = 0 V V_{DIAG_EN} = 0 V
R_{OUT} = 1 kΩ

图 27. I_{IL} vs Temperature



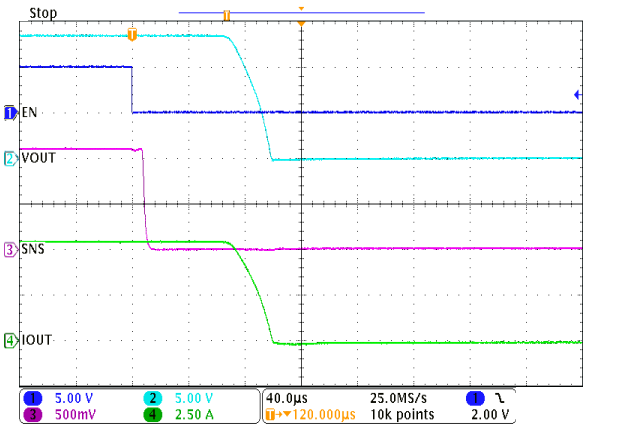
V_{EN} = 2 V V_{OUT} = 0 V V_{DIAG_EN} = 0 V
R_{OUT} = 1 kΩ

图 28. I_{IH} vs Temperature



R_{OUT} = 2.6 Ω R_{SNS} = 1 kΩ V_{DIA_EN} = 5 V
V_{SEL1} = V_{SEL2} = 0 V

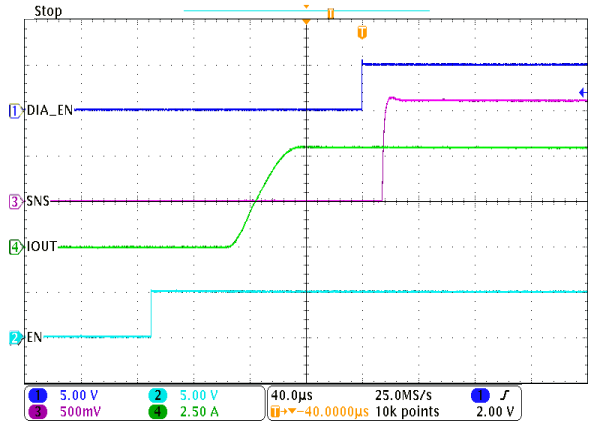
图 29. Turn-on Time (t_{ON})



R_{OUT} = 2.6 Ω R_{SNS} = 1 kΩ V_{DIA_EN} = 5 V
V_{SEL1} = V_{SEL2} = 0 V

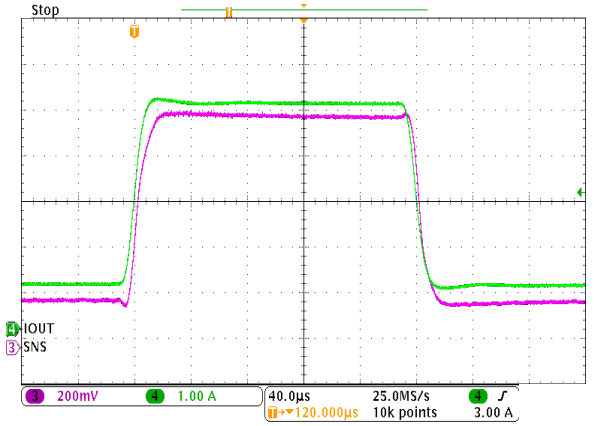
图 30. Turn-off Time (t_{OFF}) and Sense Settle Time ($t_{SNSION2}$)

Typical Characteristics (接下页)



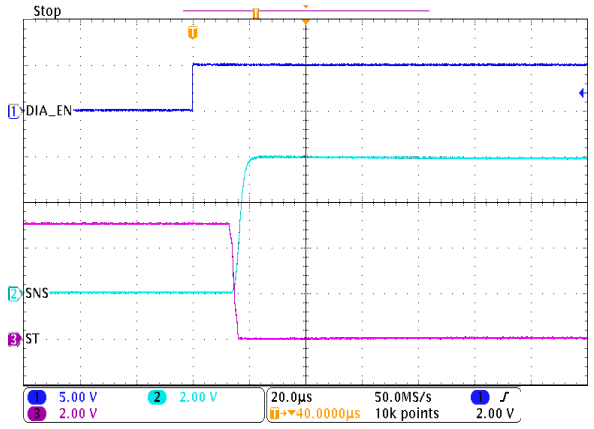
R_{OUT} = 2.6 Ω　　R_{SNS} = 1 kΩ　　V_{DIA_EN}= 0 V to 5 V
V_{SEL1} = V_{SEL2} = 0 V

图 31. I_{SNS} Settling Time ($t_{SNSION1}$) on DIA_EN Transition



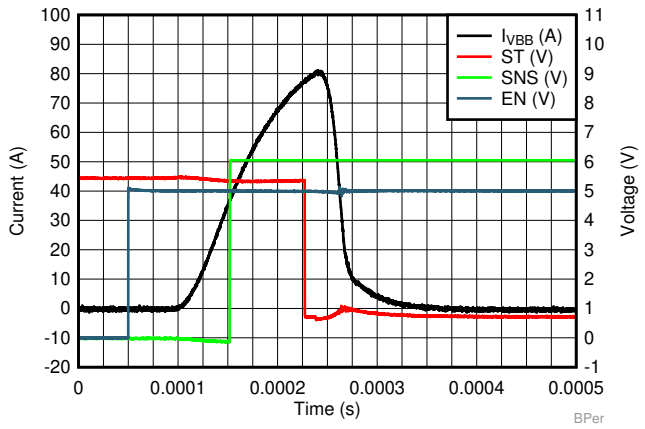
I_{OUT} = 1 A to 5 A　　R_{SNS} = 1 kΩ　　V_{DIA_EN} = 5 V
V_{SEL1} = V_{SEL2} = 0 V

图 32. I_{SNS} Settling Time ($t_{SETTLEH}$) on Rising Load Step



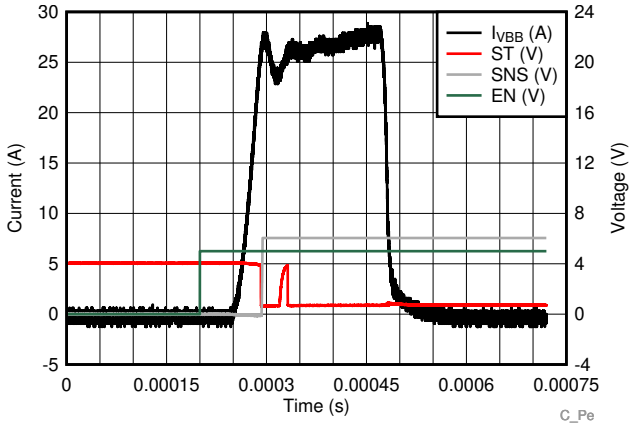
V_{OUT} = V_{BB}　　R_{SNS} = 1 kΩ　　V_{SEL1} = V_{SEL2} = 0 V
V_{EN} = 0 V　　V_{DIAG_EN} = 5 V

图 33. Open Load Detection Time (t_{OL2}) on Rising DIAG_EN



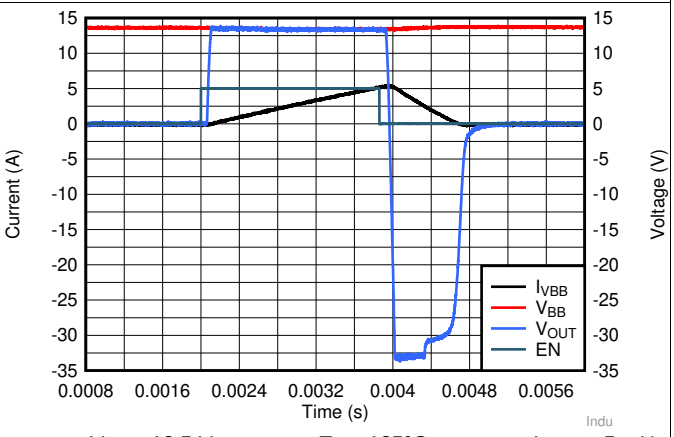
V_{BB} = 13.5 V　　B Device Version　　V_{OUT} = 0 V
V_{EN} = 0 V to 5 V　　T_A = 25°C

图 34. Short Circuit Behavior with B Device Version



V_{BB} = 13.5 V　　C Device Version　　V_{OUT} = 0 V
V_{EN} = 0 V to 5 V　　T_A = 25°C

图 35. Short Circuit Behavior with C Device Version



V_{BB} = 13.5 V　　T_A = 125°C　　L_{OUT} = 5 mH
V_{EN} = 0 V to 5 V, 5 V to 0 V

图 36. Inductive Load Demagnetization

8 Parameter Measurement Information

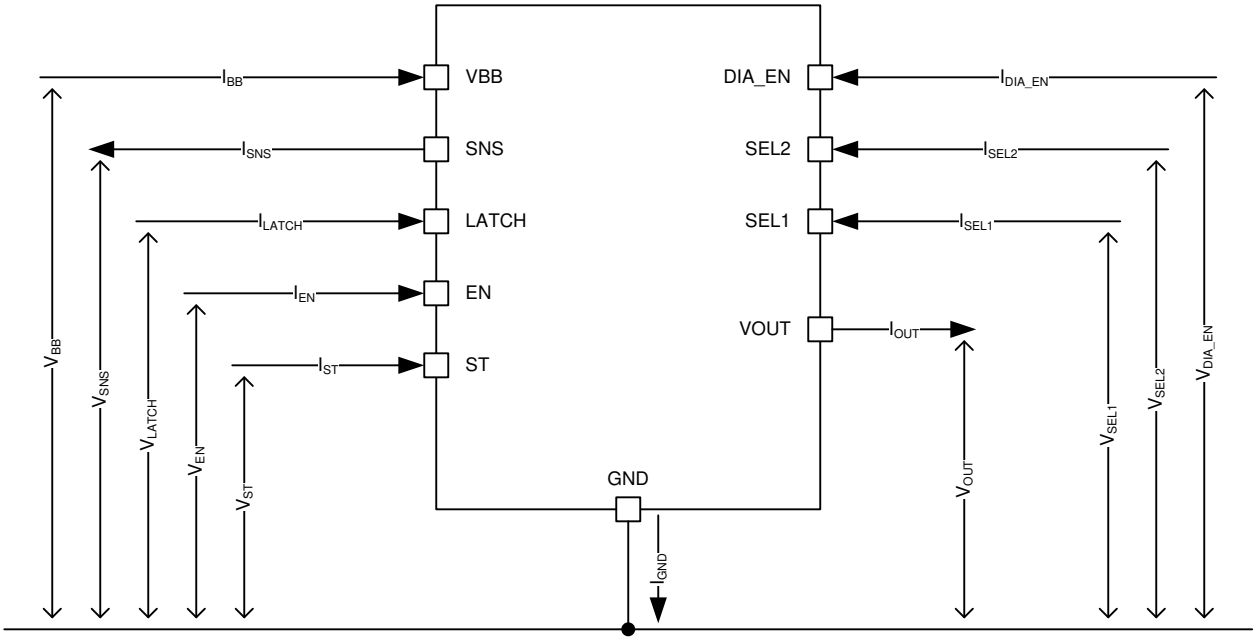


图 37. Parameter Definitions

9 Detailed Description

9.1 Overview

The device is a single-channel smart high-side power switch intended for use with 12 V automotive batteries. Many protection and diagnostic features are integrated in the device.

Diagnostics features include the analog SNS output and the open-drain fault indication ($\overline{ST}$). The analog SNS output is capable of providing a signal that is proportional to device temperature, supply voltage, or load current. The high-accuracy load current sense allows for diagnostics of complex loads.

This device includes protection through thermal shutdown, current limit, transient withstand, and reverse battery operation. For more details on the protection features, refer to the *Feature Description* and *Application Information* sections of the document.

9.1.1 Device Nomenclature

The is one device in the TI family of Smart High Side Switches. 图 38 shows the family part number nomenclature and explains how to determine device characteristics from the part number for TI Smart High Side Switches.

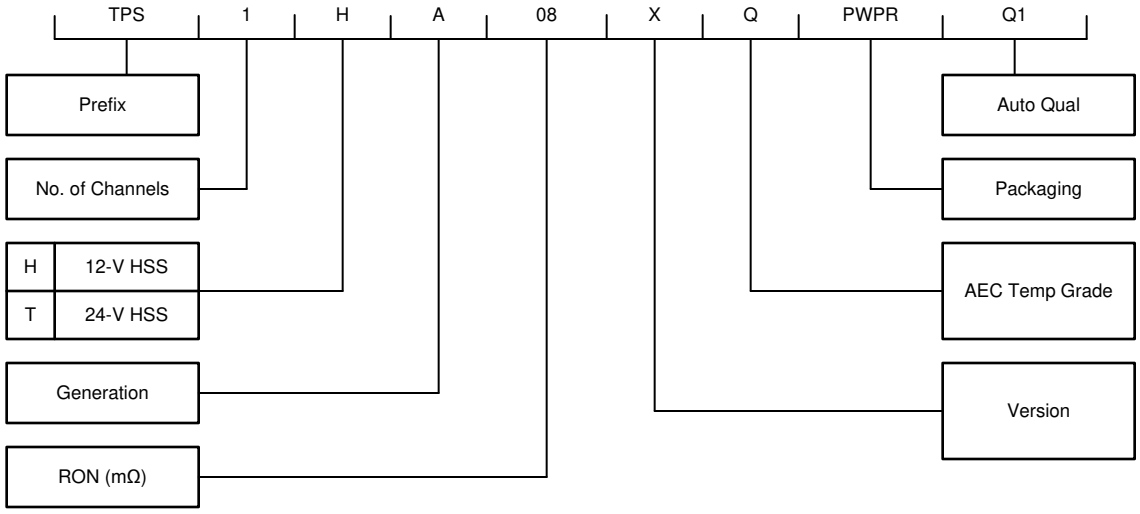
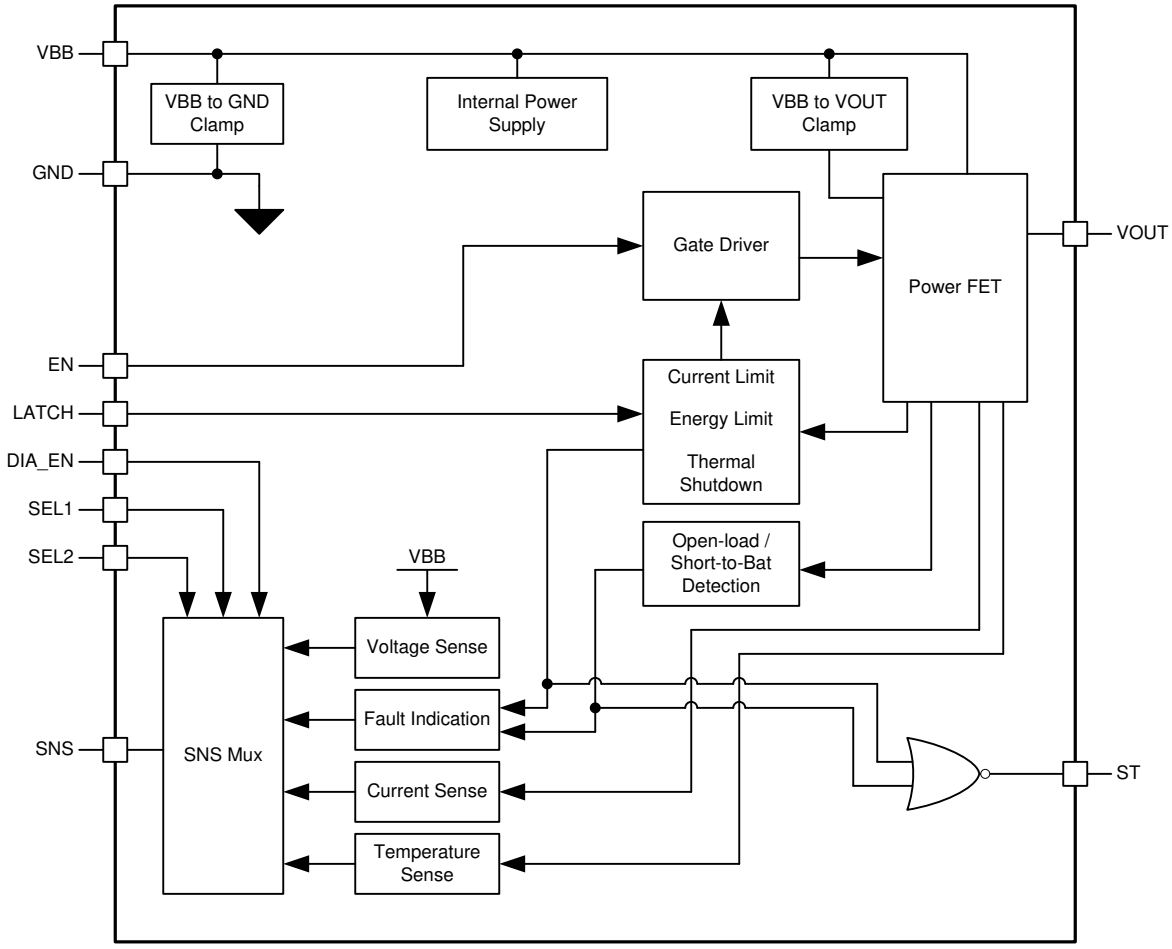


图 38. Naming Convention

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Protection Mechanisms

The is designed to operate in the automotive environment. The protection mechanisms allow the device to be robust against many system-level events such as load dump, reverse battery, short-to-ground and more.

There are three protection features which, if triggered, will cause the switch to automatically disable:

- Thermal Shutdown
- Current Limit (Versions A,B,E)
- Energy Limit

When any of these protections are triggered, the device will enter the FAULT state. In the FAULT state, the fault indication will be available on both the SNS pin and the $\overline{ST}$ pin (see the diagnostic section of the data sheet for more details).

The switch is no longer held off and the fault indication is reset when all of the below conditions are met:

- LATCH pin is low
- t_{RETRY} has expired
- All faults are cleared (thermal shutdown, current limit, energy limit)

9.3.1.1 Thermal Shutdown

The includes temperature sensors on the FET and inside of the device controller. When $T_{J,FET} > T_{ABS}$, the device will see a thermal shutdown fault. After the fault is detected, the switch will turn off. The fault is cleared when the switch temperature decreases by the hysteresis value, T_{HYS}.

9.3.1.2 Current Limit

When I_{OUT} reaches the current limit threshold, I_{CL}, the device can switch off immediately (Versions A,B,E), or the device can remain enabled and limit I_{OUT} (Versions C/D) to I_{CL} (see *Device Comparison Table* section for more details). In the case that the device remains enabled and limits I_{OUT}, the thermal shutdown and/or energy limit protection feature may be triggered due to the high amount of power dissipation in the device.

During a short circuit event, the device will hit the I_{CL} threshold that is listed in the *Specifications* (for the given device version) and then turn the output off or regulate the output current to protect the device. The device will register a short circuit event when the output current exceeds I_{CL}, however the measured maximum current may exceed the I_{CL} threshold due to the deglitch filter and turn-off time. The device is guaranteed to protect itself during a short circuit event over the nominal supply voltage range (as defined in the *Specifications* section) at 125°C.

9.3.1.2.1 Current Limit Foldback

The implements a current limit foldback feature that is designed to protect the device in the case of a long-term fault condition. If the device undergoes three consecutive fault shutdown events (any of thermal shutdown, current limit, or energy limit), the current limit will be reduced to half of the original value. The device will revert back to the original current limit threshold if either of the following occurs:

- The device goes to *Standby Delay*.
- The switch turns-on and turns-off without any fault occurring.

9.3.1.2.2 Selectable Current Limit Threshold

The offers two current limit thresholds. The high threshold is designed to allow for a large transient load current (for example, inrush current of a 65-W bulb). The low threshold is designed to provide improved system-level protection for loads that do not have large transient currents (for example, heating element). The lower threshold can allow for reduced size/cost in the current carrying components such as PCB traces and module connectors. Version A (20 A current limit) is ideal for charging capacitors, as it will enable the device to prevent inrush current and clamp the overcurrent to linearly charge the capacitor.

Feature Description (接下页)

9.3.1.2.3 Undervoltage Lockout (UVLO)

The device monitors the supply voltage V_{BB} to prevent unpredicted behaviors in the event that the supply voltage is too low. When the supply voltage falls down to V_{UVLOF}, the output stage is shut down automatically. When the supply rises up to V_{UVLOR}, the device turns back on.

During an initial ramp of V_{BB} from 0 V at a ramp rate slower than 1 V/ms, V_{EN} pin will have to be held low until V_{BB} is above UVLO threshold (with respect to board ground) and the supply voltage to the device has reliably reached above the UVLO condition. For best operation, ensure that V_{BB} has risen above UVLO before setting the V_{EN} pin to high.

9.3.1.2.4 V_{BB} during Short-to-Ground

When V_{OUT} is shorted to ground, the module power supply (V_{BB}) can have a transient decrease. This is caused by the sudden increase in current flowing through the wiring harness cables. To achieve ideal system behavior, it is recommended that the module maintain V_{BB} > 3 V during V_{OUT} short-to-ground. This is typically accomplished by placing bulk capacitance on the power supply node.

9.3.1.3 Energy Limit

The energy limiting feature is implemented to protect the switch from excessive stress. The device will continuously monitor the amount of energy dissipated in the FET. If the energy limit threshold is reached, the switch will automatically disable. In practice, the energy limit will only be reached during a fault event such as short-to-ground.

Energy limit events have the same system-level behavior as thermal shutdown events.

9.3.1.4 Voltage Transients

The contains two voltage clamps which protect the device against system-level voltage transients.

The clamp from V_{BB} to GND is primarily used to protect the controller from positive transients on the supply line (for example, ISO7637-2). The clamp from V_{BB} to V_{OUT} is primarily used to limit the voltage across the FET when switching off an inductive load. Both clamp levels are set to protect the device during these fault conditions. If the voltage potential from V_{BB} to GND exceeds the V_{BB} clamp level, the clamp will allow current to flow through the device from V_{BB} to GND (Path 2). If the voltage potential from V_{BB} to V_{OUT} exceeds V_{CLAMP}, the power FET will allow current to flow from V_{BB} to V_{OUT} (Path 3).

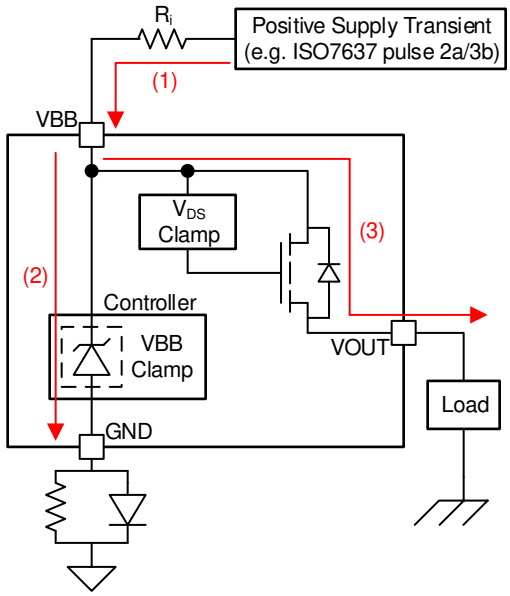


图 39. Current Path During Supply Voltage Transient

Feature Description (接下页)

9.3.1.4.1 Load Dump

The is tested according to ISO 16750-2:2010(E) suppressed load dump pulse. The device supports up to 40 V load dump transient. The switch will maintain normal operation during the load dump pulse. If the switch is enabled, it will stay enabled. If the switch is disabled, it will stay disabled.

9.3.1.4.2 Driving Inductive and Capacitive Loads

When switching off an inductive load, the inductor may impose a negative voltage on the output of the switch. The includes a voltage clamp to limit voltage across the FET. The maximum acceptable load inductance is a function of the device robustness. With a 5 mH load, the can withstand a single pulse of 95 mJ inductive dissipation at 125°C and can withstand 56 mJ of inductive dissipation with a 10 Hz repetitive pulse. If the application parameters exceed this device limit, it is necessary to use a protection device like a freewheeling diode to dissipate the energy stored in the inductor. 图 40 shows the discharging a 5 mH load that is driven at 5 A.

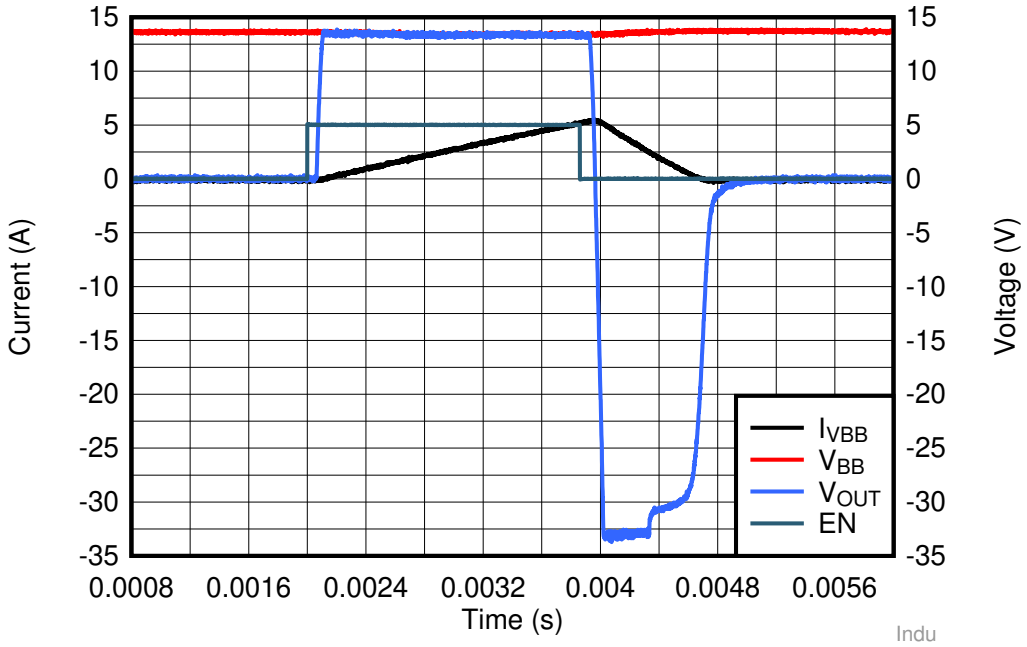


图 40. Inductive Discharge (5 mH, 5 A)

In addition, the current limit provides an ideal way to charge a capacitive load safely with limited inrush current. With no protection, charging a large capacitive load can lead to high inrush currents that pull a supply down, however by using the low current limit device options the capacitive load can be safely charged.

For more information on driving inductive or capacitive loads, reference *TI's "How To Drive Inductive, Capacitive, and Lighting Loads with Smart High Side Switch* application report.

9.3.1.5 Reverse Battery

In the reverse battery condition, the switch will automatically be enabled (regardless of EN status) to prevent power dissipation inside the MOSFET body diode. In many applications (for example, resistive load), the full load current may be present during reverse battery. In order to activate the automatic switch on feature, the SEL2 pin must have a path to module ground. This may be path 1 as shown below, or, if the SEL2 pin is unused, the path may be through R_{PROT} to module ground.

Protection features (for example, thermal shutdown) are not available during reverse battery. Care must be taken to ensure that excessive power is not dissipated in the switch during the reverse battery condition.

Feature Description (接下页)

There are two options for blocking reverse current in the system. Option 1 is to place a blocking device (FET or diode) in series with the battery supply. This will block all current paths. Option 2 is to place a blocking diode in series with the GND node of the high-side switch. This method will protect the controller portion of the switch (path 2), but it will not prevent current from flowing through the load (path 3). The diode used for Option 2 may be shared amongst multiple high-side switches.

Path 1 shown in 图 41 is blocked inside of the device.

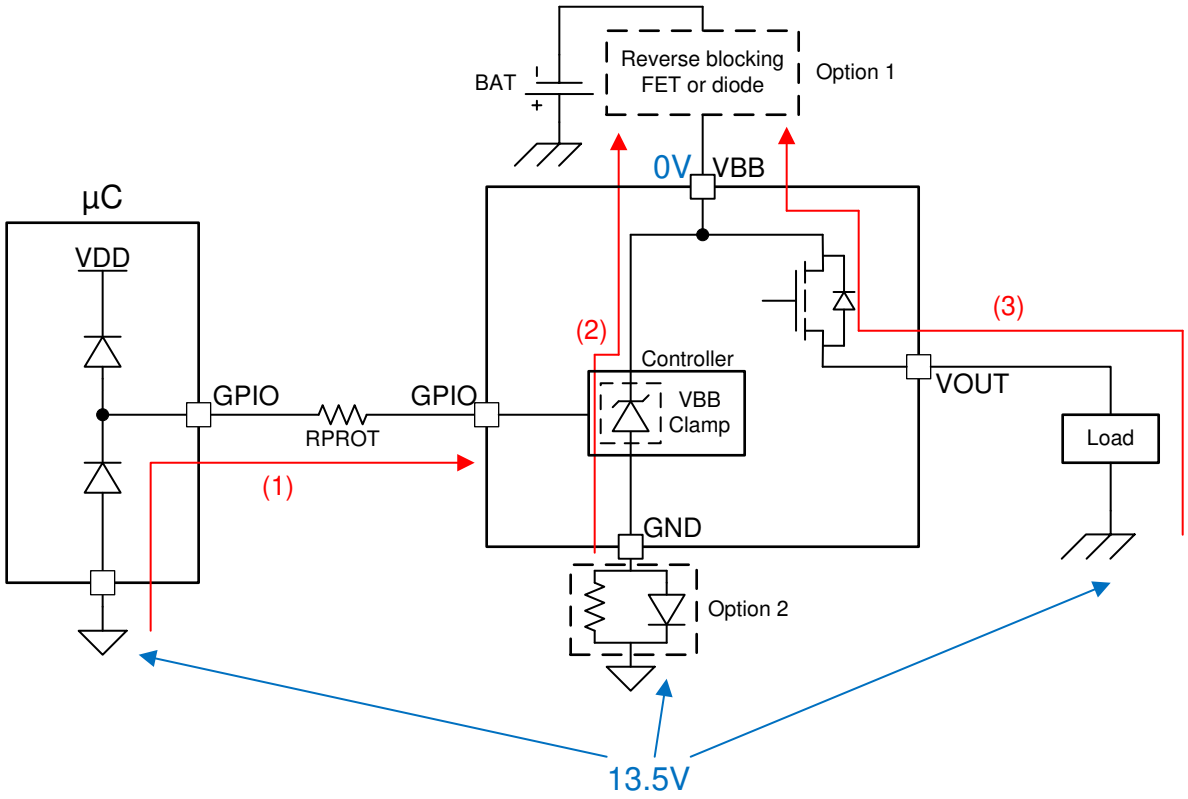


图 41. Current Path During Reverse Battery

9.3.1.6 Fault Event – Timing Diagrams

注

All timing diagrams assume that the SELx pins are set to 00.

The LATCH, DIA_EN, and EN pins are controlled by the user. The timing diagrams represent a possible use-case.

图 42 shows the immediate current limit switch off behavior of Versions A,B,E. The diagram also illustrates the retry behavior. As shown, the switch will remain latched off until the LATCH pin is low.

Feature Description (接下页)

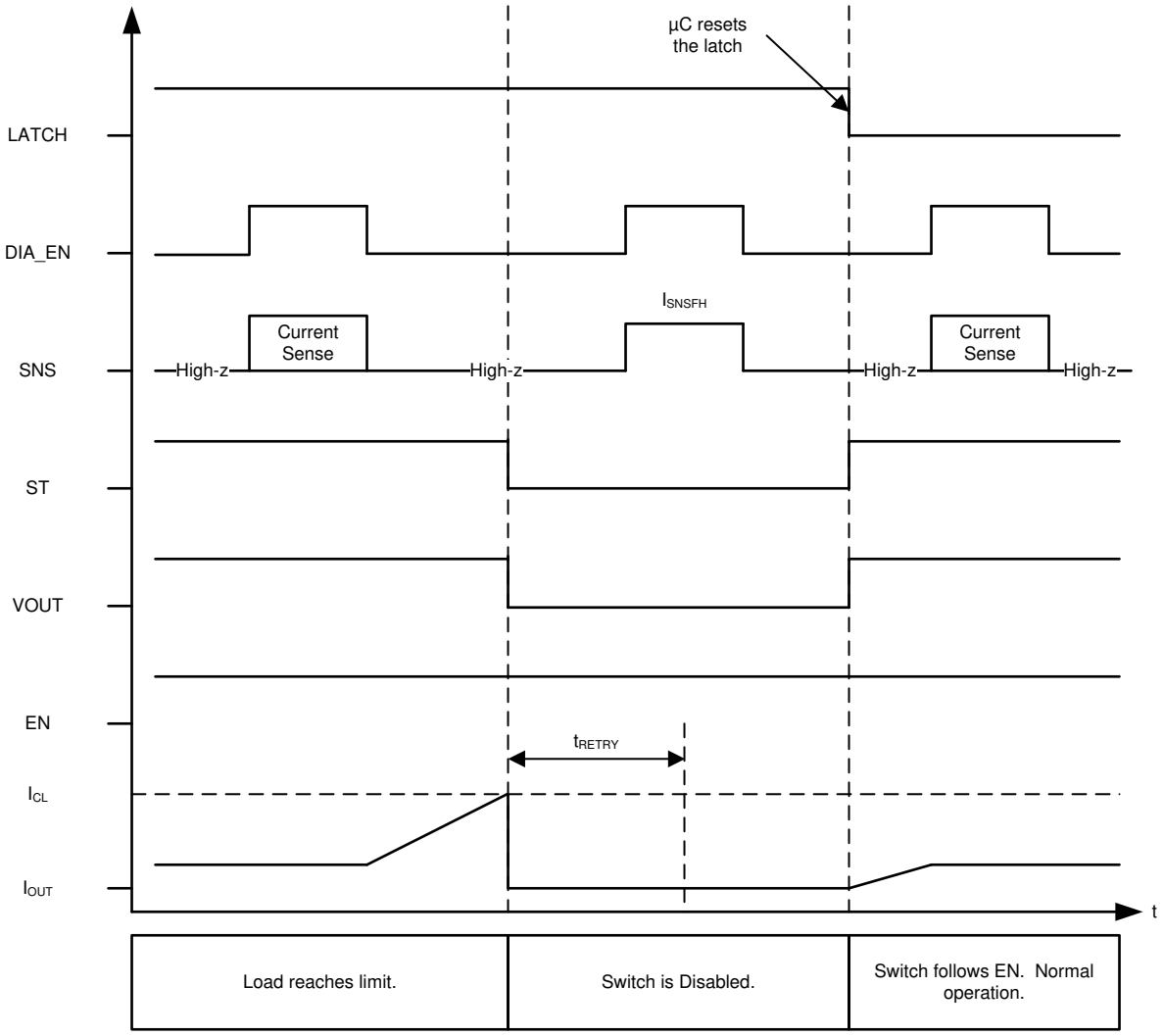


图 42. Current Limit – Version A,B,E - Latched Behavior

图 43 shows the immediate current limit switch off behavior of versions A,B,E. In this example, LATCH is tied to GND; hence, the switch will retry after the fault is cleared and t_{RETRY} has expired.

Feature Description (接下页)

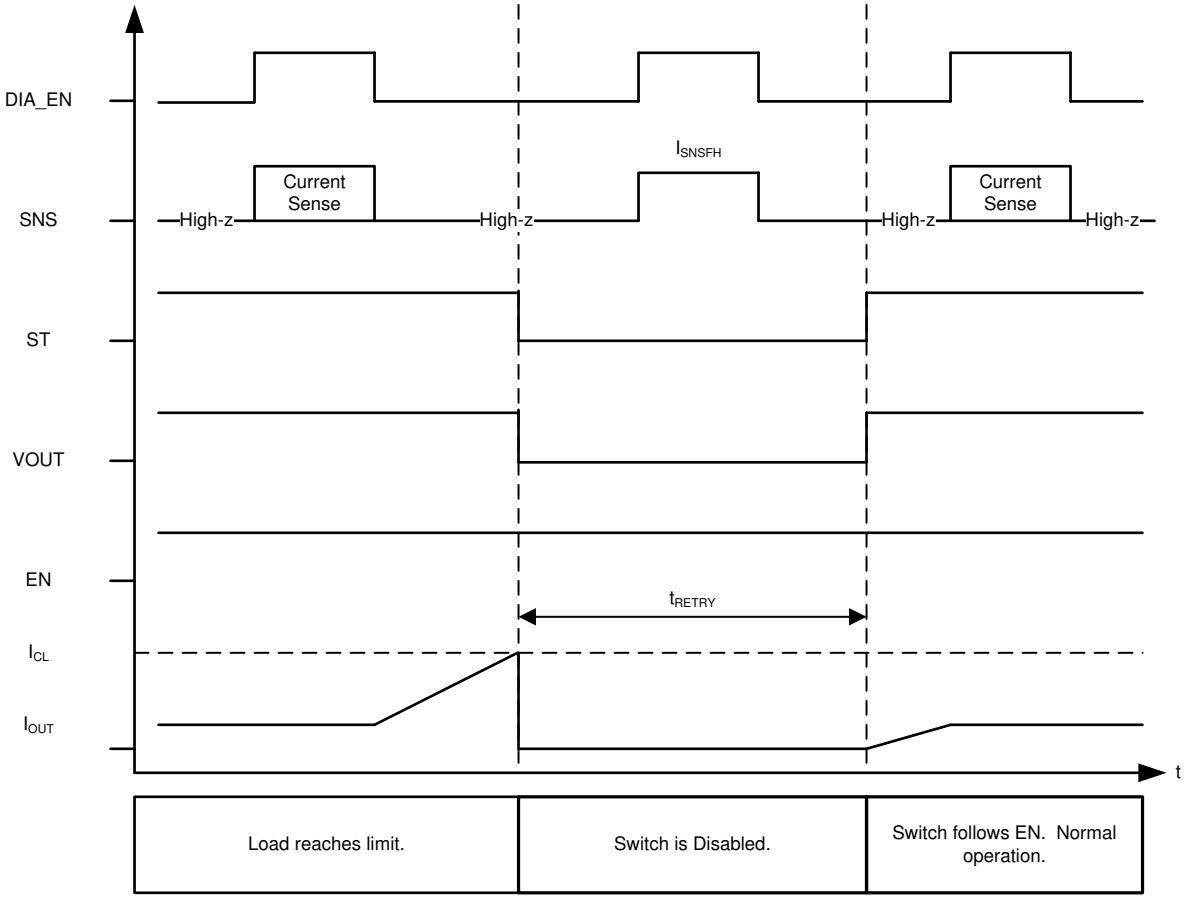


图 43. Current Limit – Version A,B,E - LATCH = 0

图 44 shows the active current limiting behavior of versions C,D. In versions C,D, the switch will not shutdown until either the energy limit or the thermal shutdown is reached.

Feature Description (接下页)

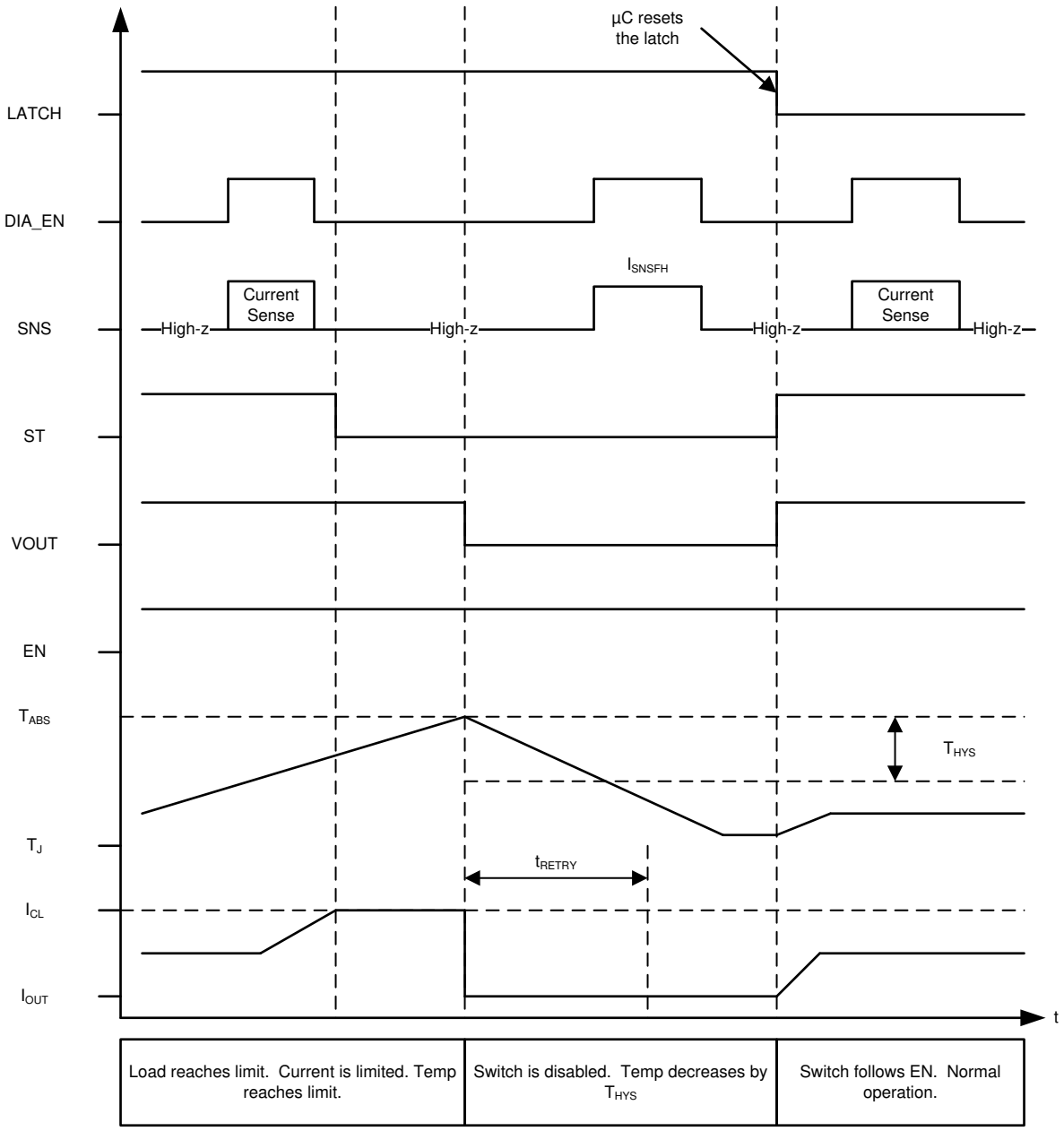


图 44. Current Limit – Version C,D - Latched Behavior

图 45 shows the active current limiting behavior of versions C,D. The switch will not shutdown until either thermal shutdown or energy limit is tripped. In this example, LATCH is tied to GND.

Feature Description (接下页)

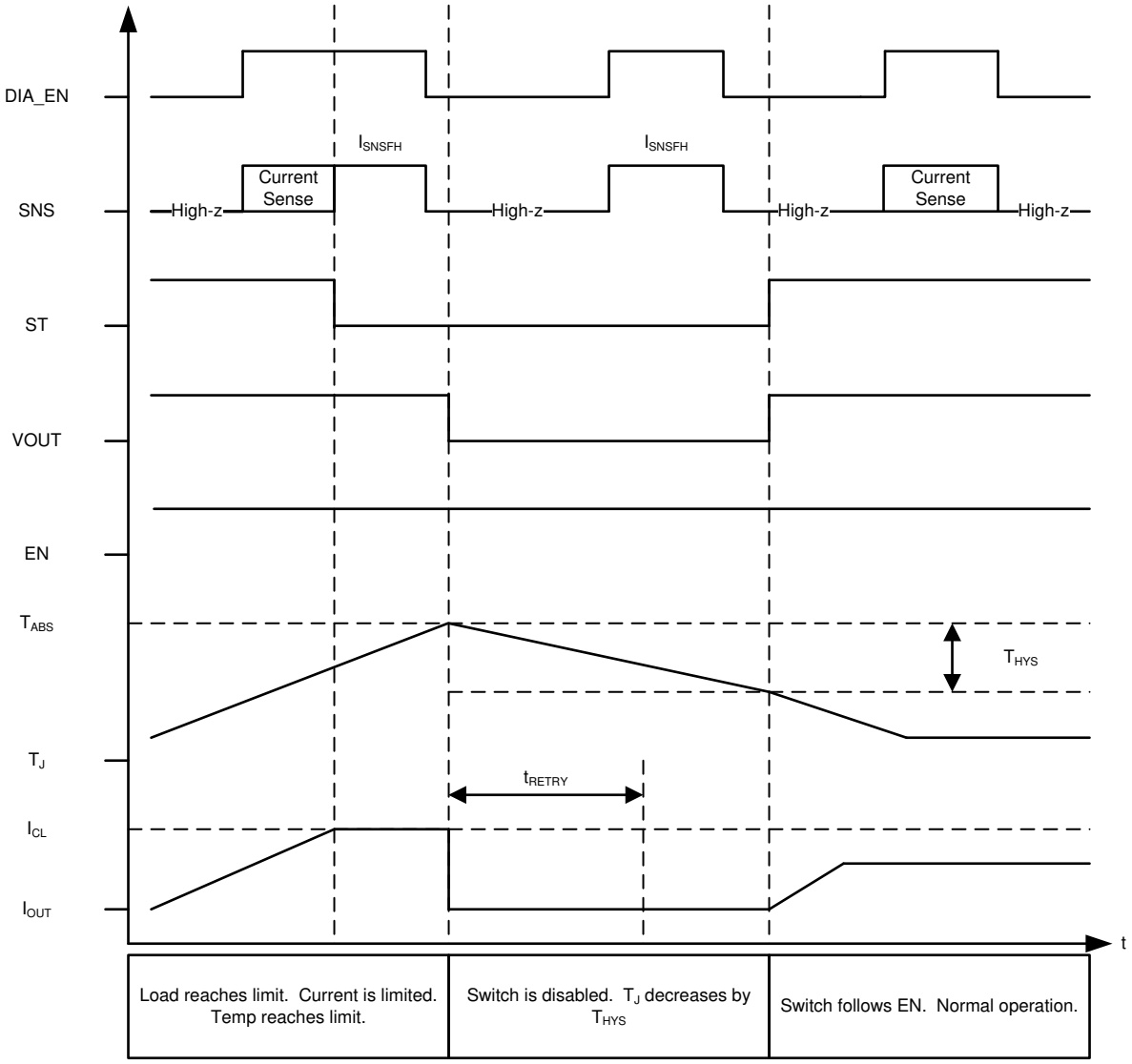


图 45. Current Limit – Version C,D - LATCH = 0

When the switch retries after a shutdown event, the SNS fault indication will remain until V_{OUT} has risen to V_{BB} – 1.8 V. Once V_{OUT} has risen, the SNS fault indication is reset and current sensing is available. $\overline{ST}$ fault indication is reset as soon as the switch is re-enabled (does not wait for V_{OUT} to rise). If there is a short-to-ground and V_{OUT} is not able to rise, the SNS fault indication will remain indefinitely. The following diagram illustrates auto-retry behavior and provides a zoomed-in view of the fault indication during retry.

注

图 46 assumes that t_{RETRY} has expired by the time that T_J reaches the hysteresis threshold.

LATCH = 0 V and DIA_EN = 5 V

Feature Description (接下页)

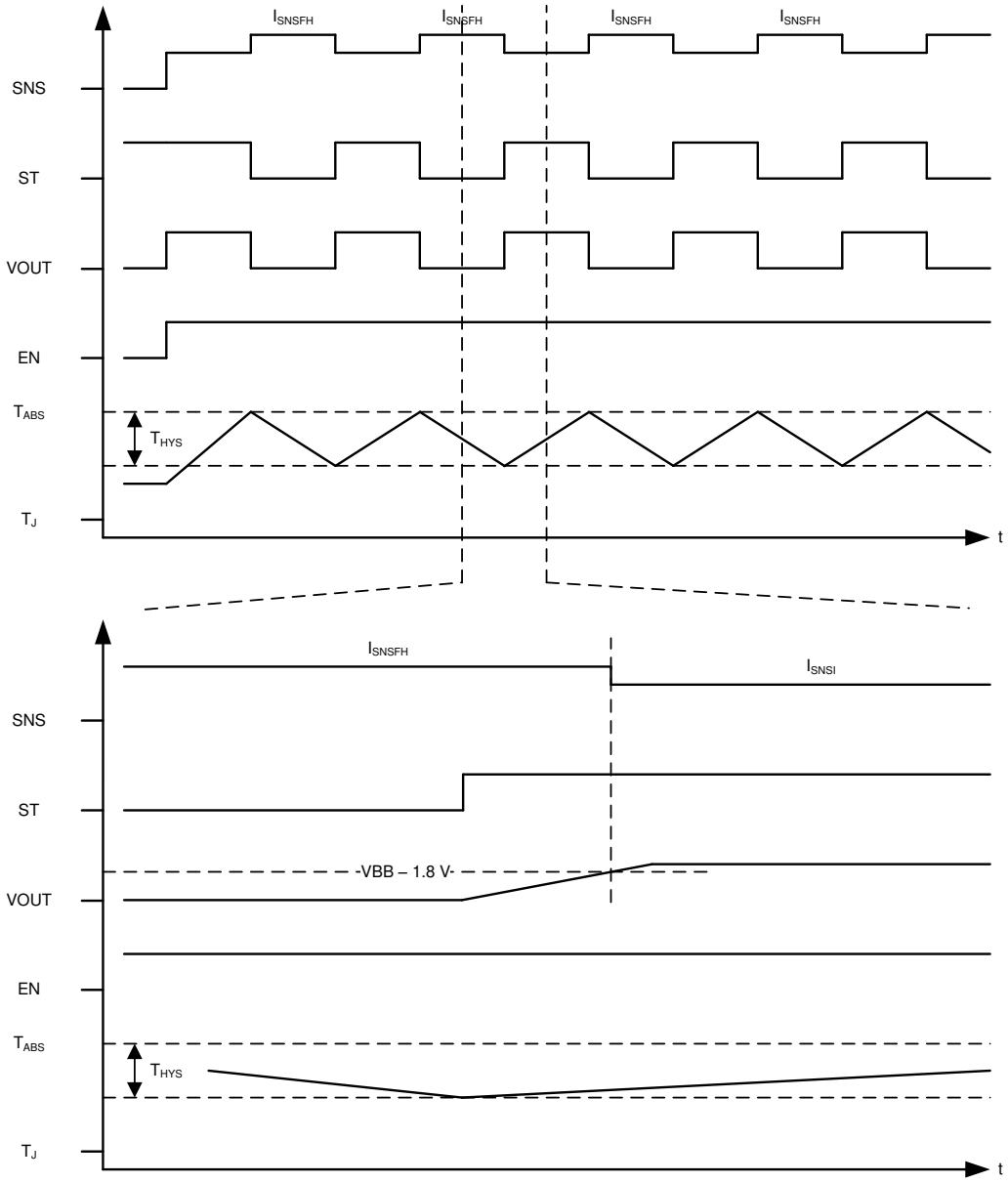


图 46. Fault Indication During Retry

9.3.2 Diagnostic Mechanisms

9.3.2.1 V_{OUT} Short-to-Battery and Open-Load

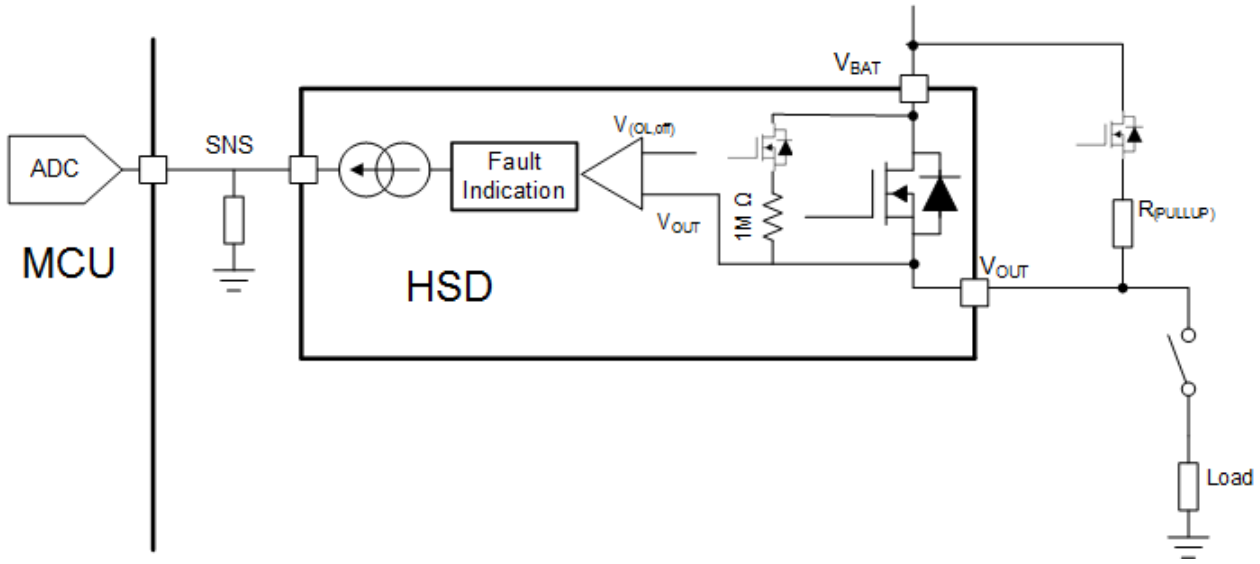
9.3.2.1.1 Detection With Switch Enabled

When the switch is enabled, the V_{OUT} short-to-battery and open-load conditions can be detected with the current sense feature. In both cases, the load current will be measured through the SNS pin and will be below the expected value.

Feature Description (接下页)

9.3.2.1.2 Detection With Switch Disabled

While the switch is disabled, if DIA_EN is high, an internal comparator will detect the condition of V_{OUT}. If the load is disconnected (open load condition) or there is a short to battery the $_{OUT}$ voltage will be higher than the open load threshold ($V_{OL,off}$) and a fault is indicated on the SNS pin. An internal pull-up of 1 MΩ is in series with an internal MOSFET switch, so no external component is required if only a completely open load needs to be detected. However, if there is significant leakage or other current draw even when the load is disconnected, a lower value pull-up resistor and switch can be added externally to set the V_{OUT} voltage above the $V_{OL,off}$ during open load conditions.



(1) This figure assumes that the device ground and the load ground are at the same potential. In application, there may be a ground shift voltage of 1 V to 2 V.

图 47. Short to Battery and Open Load Detection

The detection circuitry is only enabled when DIA_EN = HIGH and EN = LOW.

If $V_{OUT} > V_{OL}$, the SNS pin will go to the fault level.

If $V_{OUT} < V_{OL}$, then there is no fault indication.

The fault indication will only occur if the SEL1 pin is set to diagnose the channel.

While the switch is disabled and DIA_EN is high, the fault indication mechanisms will continuously represent the present status. For example, if V_{OUT} decreases from $>V_{OL}$ to $<V_{OL}$, the fault indication is reset. Additionally, the fault indication is reset upon the falling edge of DIA_EN or the rising edge of EN.

Feature Description (接下页)

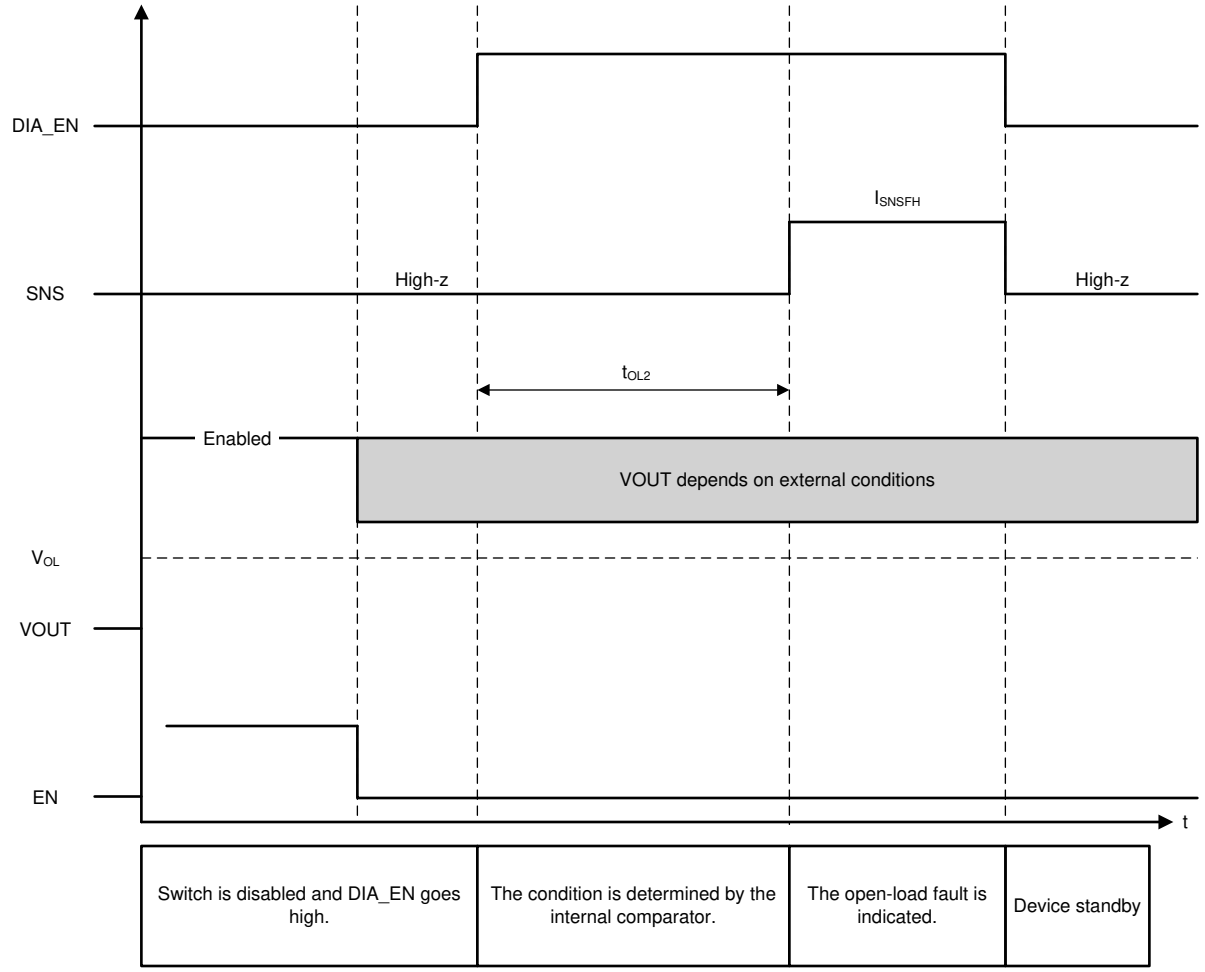


图 48. Open Load

9.3.2.2 SNS Output

The SNS output may be used to sense the load current, supply voltage, or device temperature. The SELx pins will select the desired sense signal. The sense circuit will provide a current that is proportional to the selected parameter. This current will be sourced into an external resistor to create a voltage that is proportional to the selected parameter. This voltage may be measured by an ADC or comparator.

To ensure accurate sensing measurement, the sensing resistor should be connected to the same ground potential as the μC ADC.

The SNS Output includes an internal clamp, $V_{SNSclamp}$. This clamp is designed to prevent a high voltage at the SNS output and the ADC input.

表 2. Analog Sense Transfer Function

PARAMETER	TRANSFER FUNCTION
Load current	$I_{SNSI} = I_{OUT} / 4600$
Supply voltage(1)	$I_{SNSV} = (V_{BB}) \times dI_{SNSV} / dV$
Device temperature	$I_{SNST} = (T_J – 25°C) \times dI_{SNST} / dT + 0.85$

(1) Voltage potential between the V_{BB} pin and the GND pin.

The SNS output will also be used to indicate system faults. I_{SNS} will go to the predefined level, I_{SNSFH}, when there is a fault. This level is defined in the electrical specifications.

9.3.2.2.1 R_{SNS} Value

The following factors should be considered when selecting the R_{SNS} value:

- Current sense ratio
- Largest and smallest diagnosable load current
- Full-scale voltage of the ADC
- Resolution of the ADC

For an example of selecting R_{ISNS} value, reference *Selecting the R_{ISNS} Value* in the applications section of this data sheet.

9.3.2.2.1.1 High Accuracy Load Current Sense

In many automotive modules, it is required that the high-side switch provide diagnostic information about the downstream load. With more complex loads, high accuracy sensing is required. A few examples follow:

- **LED Lighting**: In many architectures, the Body Control Module must be compatible with both incandescent bulbs and also LED modules. The bulb may be relatively simple to diagnose. However, the LED module will consume less current and also can include multiple LED strings in parallel. The same BCM is used in both cases, so the high-side switch must be able to accurately diagnose both load types.
- **Solenoid Protection**: Often solenoids are precisely controlled by low-side switches. However, in a fault event, the low-side switch cannot disconnect the solenoid from the power supply. A high-side switch can be used to continuously monitor several solenoids. If the system current becomes higher than expected, the high-side switch can disable the module.

9.3.2.2.1.2 SNS Output Filter

To achieve the most accurate current sense value, it is recommended to apply filtering to the SNS output. There are two methods of filtering:

- Low-Pass RC filter between the SNS pin and the ADC input. This filter is illustrated in 图 54 and typical values for the resistor and capacitor are given. The designer should select a C_{SNS} capacitor value based on system requirements. A larger value will provide improved filtering. A smaller value will allow for faster transient response.
- The ADC and microcontroller can also be used for filtering. It is recommended that the ADC collects several measurements of the SNS output. The median value of this data set should be considered as the most accurate result. By performing this median calculation, the microcontroller is able to filter out any noise or outlier data.

9.3.2.3 $\overline{ST}$ Pin

The $\overline{ST}$ pin is an open-drain output. The pin indicates the status of the switch channel. The output is high-z when there is no fault condition. The output is pulled low when there is a fault condition.

9.3.2.4 Fault Indication and SNS Mux

The following faults will be communicated via the SNS and $\overline{ST}$ outputs:

- Switch shutdown, due to:
  - Thermal Shutdown
  - Current limit
  - Energy limit
- Active current limiting
- Open-Load / V_{OUT} shorted-to-battery

Open-load / Short-to-battery are not indicated while the switch is enabled (though these conditions can be detected via the sense current). Hence, if there is a fault indication corresponding to an enabled channel, then it must be either switch shutdown or active current limiting.

The SNS pin will only indicate the fault if the SELx = 00. Switch shutdown fault indication will occur on the $\overline{ST}$ pin regardless of the SELx pins; however, OL/STB fault indication is only available when the SELx = 00.

表 3. SNS Mux

INPUTS				OUTPUTS	
DIA_EN	SEL1	SEL2	FAULT DETECT(1)	SNS	ST
0	X	X	0	High-z	High-z
0	X	X	1	High-z	Pull low
1	0	0	0	Load current	High-z
1	0	1	0	Not Used	Not Used
1	1	0	0	Device temperature	High-z
1	1	1	0	Supply voltage	High-z
1	0	0	1	I_{SNSFH}	Pull low
1	0	1	1	Not Used	Not Used
1	1	0	1	Device temperature	Pull low
1	1	1	1	Supply voltage	Pull low

(1) Fault Detect encompasses the below conditions:
(a) Switch shutdown and waiting for retry
(b) Active current limiting
(c) OL / STB

9.3.2.5 Resistor Sharing

Multiple high-side switch channels may use the same SNS resistor as shown in 图 49 below. This reduces the total number of passive components in the system and the number of ADC terminals that are required of the microcontroller.

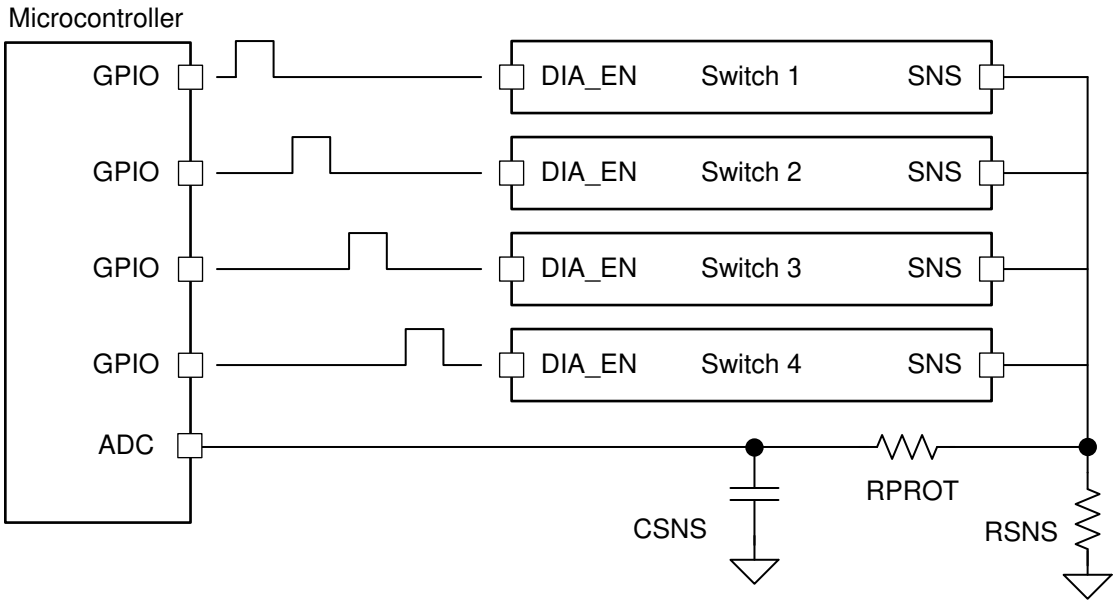


图 49. Sharing R_{SNS} Among Multiple Devices

9.3.2.6 High-Frequency, Low Duty-Cycle Current Sensing

Some applications will operate with a high-frequency, low duty-cycle PWM. Such applications require fast settling of the SNS output. For example, a 250 Hz, 5% duty cycle PWM will have an on-time of only 200 µs. The microcontroller ADC may sample the SNS signal after the defined settling time, $t_{SNSION3}$.

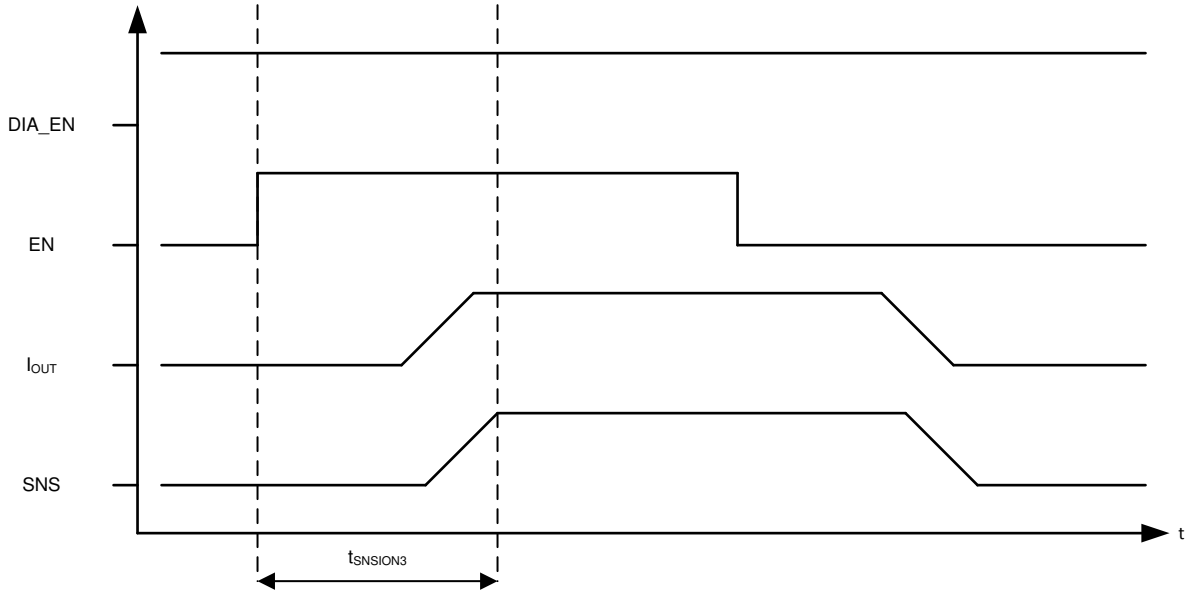
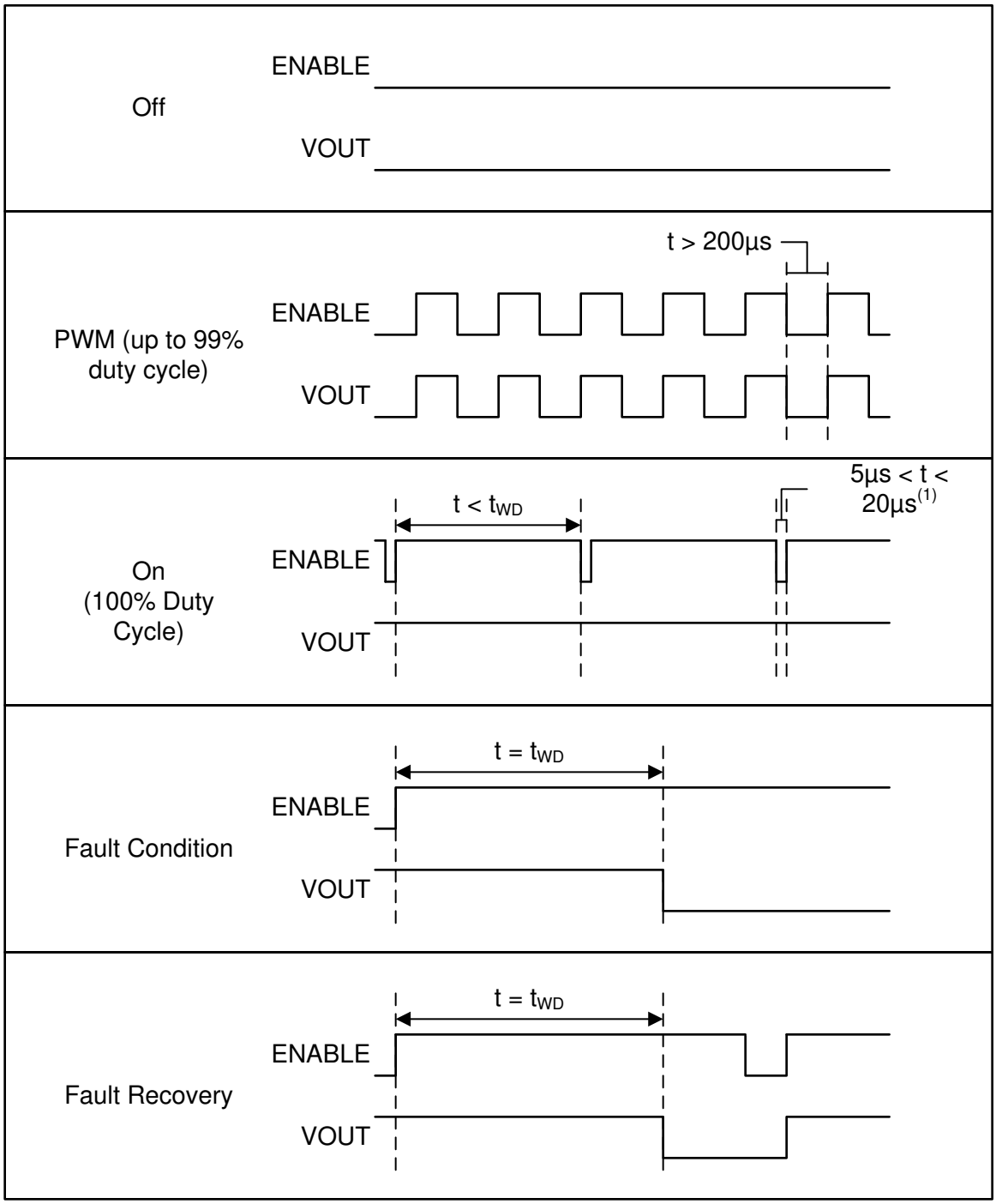


图 50. Current Sensing in Low-Duty Cycle Applications

9.3.3 Enable Watchdog

For some automotive applications, it is necessary to continuously verify that there is valid communication between the microcontroller and the switch enable pin. The purpose of this is to protect against possible communication faults (for example, microcontroller failure). The \ includes an optional watchdog feature which continuously polls the enable pin. Note that this feature is only activated for device version E, so the below information is only applicable to version E.

To use the watchdog feature, the microcontroller should apply a PWM to the switch enable pin. If this PWM is not present (EN is high continuously for ≥ t_{WD}) the switch will automatically be disabled. The watchdog timer is reset on the rising edge of EN. The fault indications are cleared upon the falling edge of EN. The following figure illustrates how the switch will respond to the EN PWM.



The watchdog feature requires that a PWM is applied to the switch enable pin. To maintain V_{OUT} at 100% duty cycle, the microcontroller should periodically apply a short pulse to the enable pin. This short pulse will reset the watchdog timer, but will not cause the switch to turn-off. The pulse must be >5 µs to ensure that it is recognized by the device. There is no upper limit on the pulse width; however, if the pulse is longer than 20 µs, the switch may start to transition from enabled to disabled.

图 51. Enable Watchdog - Overview

图 52 illustrates the behavior of the watchdog feature.

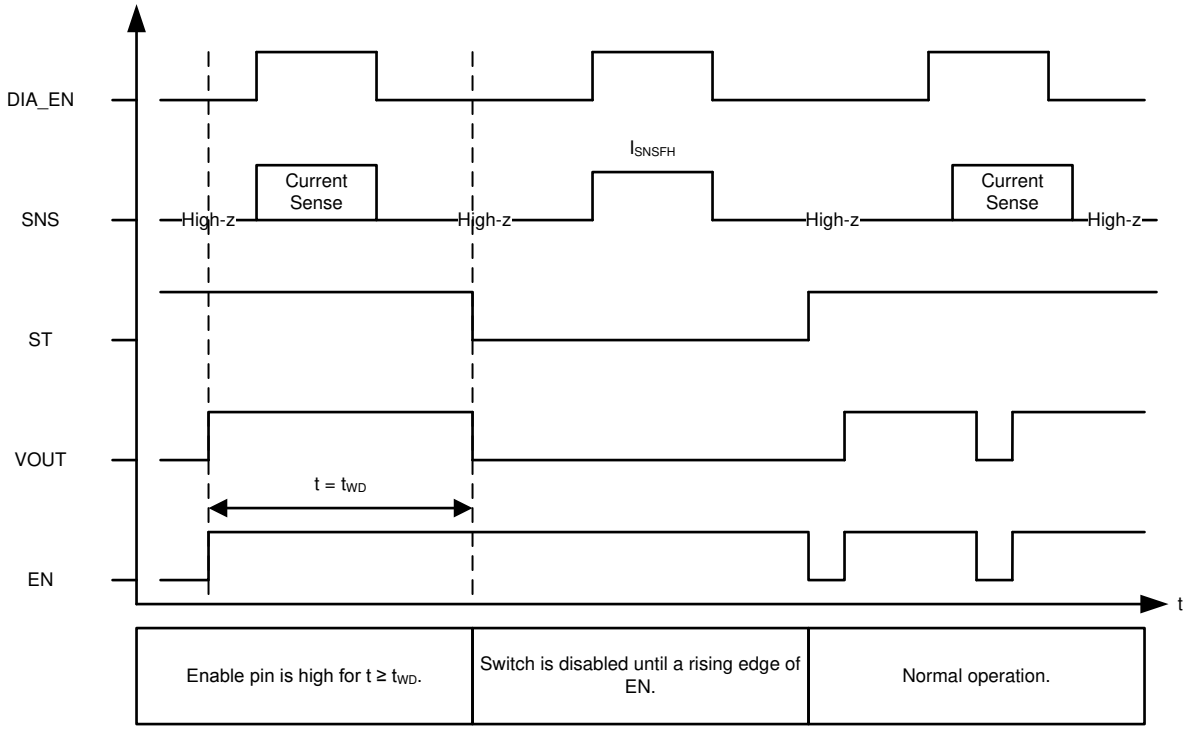


图 52. Enable Watchdog Timing Diagram

9.4 Device Functional Modes

9.4.1 Off

Off state occurs when the device is not powered.

9.4.2 Standby

Standby state is a low-power mode used to reduce power consumption to the lowest level. Diagnostic capabilities are not available in Standby mode.

9.4.3 Diagnostic

Diagnostic state may be used to perform diagnostics while the switch is disabled.

9.4.4 Standby Delay

The Standby Delay state is entered when EN and DIA_EN are low. After t_{STBY}, if the EN and DIA_EN pins are still low, the device will go to Standby State.

9.4.5 Active

In Active state, the switch is enabled. The diagnostic functions may be turned on or off during Active state.

9.4.6 Fault

The Fault state is entered if a fault shutdown occurs (thermal shutdown, current limit, energy limit). After all faults are cleared, the LATCH pin is low, and the retry timer has expired, the device will transition out of Fault state. If the Enable pin is high, the switch will re-enable. If the Enable pin is low, the switch will remain off.

Device Functional Modes (接下页)

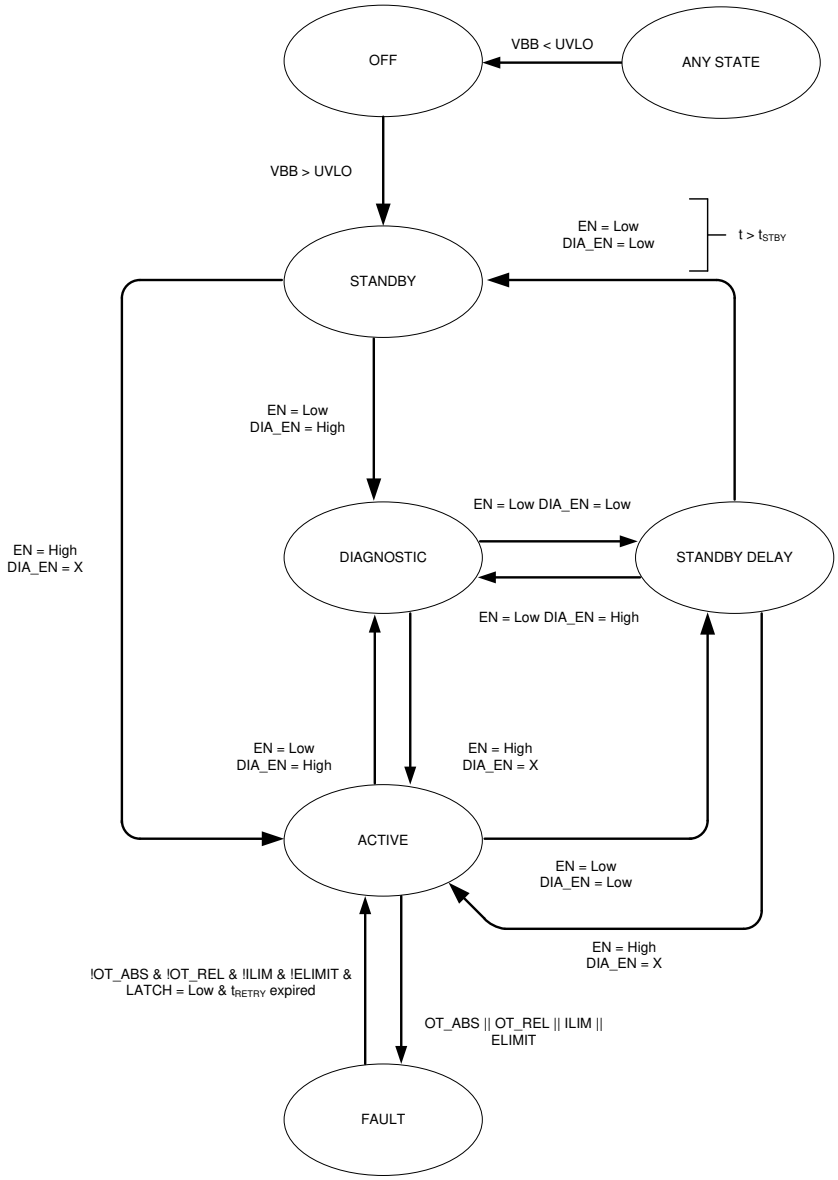


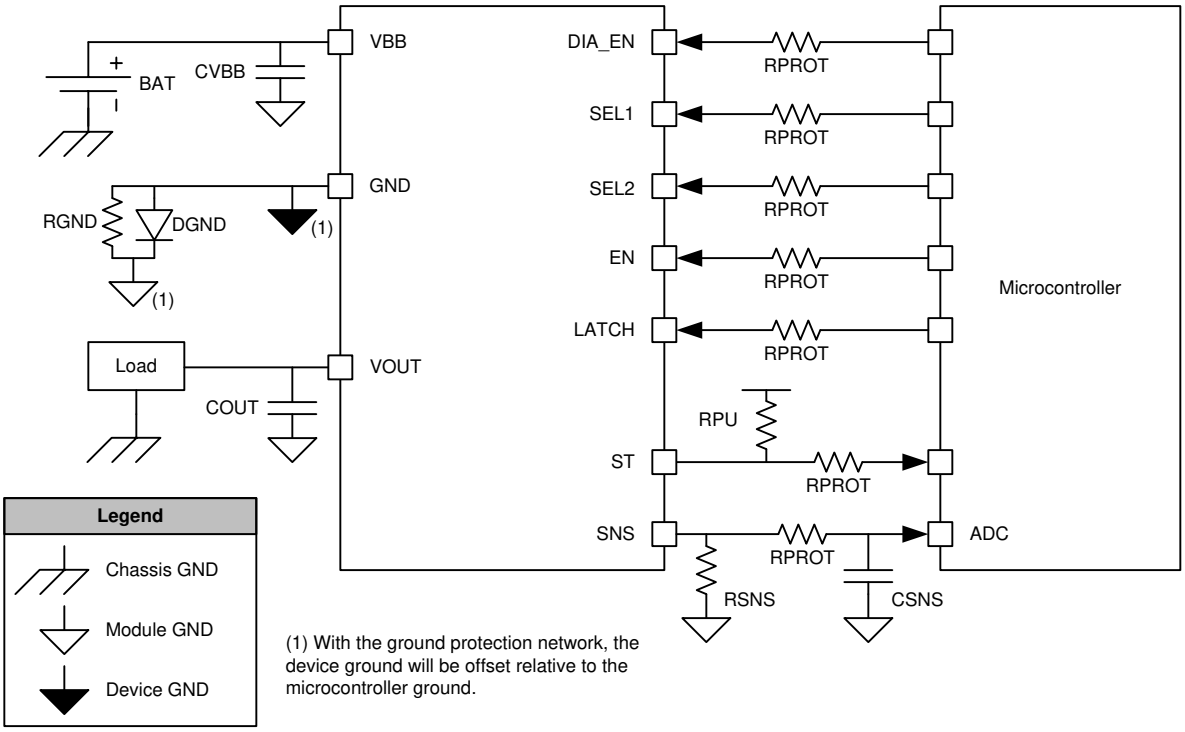
图 53. State Diagram

10 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information



With the ground protection network, the device ground will be offset relative to the microcontroller ground.

图 54. System Diagram

表 4. Recommended External Components

COMPONENT	TYPICAL VALUE	PURPOSE
R_{PROT}	15 kΩ	Protect microcontroller and device I/O pins
R_{SNS}	1 kΩ	Translate the sense current into sense voltage
R_{PU}	10 kΩ	Provide pull-up source for open-drain output
C_{SNS}	100 pF - 10 nF	Low-pass filter for the ADC input
R_{GND}	4.7 kΩ	Stabilize GND potential during turn-off of inductive load
D_{GND}	BAS21 Diode	Protects device during reverse battery
C_{VBB}	220 nF to Device GND	Filtering of voltage transients (for example, ESD, ISO7637-2) and improved emissions
	100 nF to Module GND	Stabilize the input supply and filter out low frequency noise.
C_{OUT}	22 nF	Filtering of voltage transients (for example, ESD, ISO7637-2)

10.1.1 Ground Protection Network

As discussed in the section regarding Reverse Battery, D_{GND} may be used to prevent excessive reverse current from flowing into the device during a reverse battery event. Additionally, R_{GND} is placed in parallel with D_{GND} if the switch is used to drive an inductive load. The ground protection network (D_{GND} and R_{GND}) may be shared amongst multiple high-side switches.

A minimum value for R_{GND} may be calculated by using the absolute maximum rating for I_{GND}. During the reverse battery condition, $I_{GND} = V_{BB} / R_{GND}$:

$R_{GND} \geq V_{BB} / I_{GND}$

- Set V_{BB} = –13.5 V
- Set I_{GND} = –50 mA (absolute maximum rating)

$$R_{GND} \geq –13.5\ V / –50\ mA = 270\ \Omega \quad (1)$$

In this example, it is found that R_{GND} must be at least 270 Ω. It is also necessary to consider the power dissipation in R_{GND} during the reverse battery event:

$$P_{RGND} = V_{BB}^2 / R_{GND} \quad (2)$$

$$P_{RGND} = (13.5\ V)^2 / 270\ \Omega = 0.675\ W$$

In practice, R_{GND} may not be rated for such a high power. In this case, a larger resistor value should be selected.

10.1.2 Interface With Microcontroller

The ground protection network will cause the device ground to be at a higher potential than the module ground (and microcontroller ground). This offset will impact the interface between the device and the microcontroller.

Logic pin voltage will be offset by the forward voltage of the diode. For input pins (for example, EN), the designer must consider the V_{IH} specification of the switch and the V_{OH} specification of the microcontroller. For a system that *does not* include D_{GND}, it is required that $V_{OH} > V_{IH}$. For a system that *does* include D_{GND}, it is required that $V_{OH} > (V_{IH} + V_F)$. V_F is the forward voltage of D_{GND}.

For use of the status pin, ST, a similar consideration is necessary. The designer must consider the $V_{OL,\ ST}$ specification and the V_{IL} specification of the microcontroller. For a system that includes DGND, it is required that $V_{OL,\ ST} + V_F < V_{IL,\ \mu C}$.

The sense resistor, R_{SNS}, should be terminated to the microcontroller ground. In this case, the ADC can accurately measure the SNS signal even if there is an offset between the microcontroller ground and the device ground.

10.1.3 I/O Protection

R_{PROT} is used to protect the microcontroller I/O pins during system-level voltage transients such as ISO pulses or reverse battery. A large resistance value ensures that current through the pin is limited to a safe level.

10.1.4 Inverse Current

Inverse current occurs when 0 V < V_{BB} < V_{OUT}. In this case, current may flow from V_{OUT} to V_{BB}. Inverse current cannot be caused by a purely resistive load. However, a capacitive or inductive load can cause inverse current. For example, if there is a significant amount of load capacitance and the V_{BB} node has a transient droop, V_{OUT} may be greater than V_{BB}.

will not detect inverse current. When the switch is enabled, inverse current will pass through the switch. When the switch is disabled, inverse current may pass through the MOSFET body diode. The device will continue operating in the normal manner during an inverse current event.

10.1.5 Loss of GND

The ground connection may be lost either on the device level or on the module level. If the ground connection is lost, both switches will be disabled. If the switch was already disabled when the ground connection was lost, the switch will remain disabled. When the ground is reconnected, normal operation will resume.

10.1.6 Automotive Standards

10.1.6.1 ISO7637-2

is tested according to the ISO7637-2:2011 (E) standard. The test pulses are applied both with the switches enabled and disabled. The test setup includes only the DUT and minimal external components: C_{VBB}, C_{OUT}, D_{GND}, and R_{GND}.

Status II is defined in ISO 7637-1 Function Performance Status Classification (FPSC) as: “The function does not perform as designed during the test but returns automatically to normal operation after the test”.

表 5. ISO7637-2:2011 (E) Results

TEST PULSE	TEST PULSE SEVERITY LEVEL WITH STATUS II FUNCTIONAL PERFORMANCE		MINIMUM NUMBER OF PULSES OR TEST TIME	BURST CYCLE / PULSE REPETITION TIME	
	LEVEL	US		MIN	MAX
1	IV	–150 V	500 pulses	0.5 s	--
2a	III	+55 V	500 pulses	0.20	5 s
2b	IV	+10 V	10 pulses	0.5 s	5 s
3a	III	–165 V	1 hour	90 ms	100 ms
3b	III	+112 V	1 hour	90 ms	100 ms

10.1.6.2 AEC – Q100-012 Short Circuit Reliability

The is tested according to the AEC - Q100-012 Short Circuit Reliability standard. This test is performed to demonstrate the robustness of the device against V_{OUT} short-to-ground events. Test results are summarized in 表 6. For further details, refer to the AEC - Q100-012 standard document or TI's *Short Circuit Reliability Test for Smart Power Switches* application report.

Test conditions:

- LATCH = 0 V
- T_A = –40ºC
- 10 units from 3 separate lots for a total of 30 units
- L_{supply} = 5 µH, R_{supply} = 10 mΩ
- V_{BB} = 14 V

Test procedure:

- Parametric data is collected on each unit pre-stress
- Each unit is enabled into a short circuit with the required short circuit cycles or duration as specified
- Parametric data is re-collected on each unit post-stress to verify that no parametric shift is observed

The cold repetitive test is run at –40ºC which is the worst case condition for the . The current limit threshold is highest at cold temperature; hence, the short-circuit pulse contains more energy at cold temperature. The cold repetitive test refers to the device being given time to cool down between pulses, within than being run at a cold temperature. The load short circuit is the worst case situation, since the energy stored in the cable inductance can cause additional harm. The fast response of the device ensures current limiting occurs quickly and at a current close to the load short condition. In addition, the hot repetitive test is performed as well.

表 6. AEC - Q100-012 Test Results

TEST	LOCATION OF SHORT	DEVICE VERSION	NO. OF CYCLES	NO. OF UNITS	NO. OF FAILS
Cold Repetitive - Long Pulse	Load Short Circuit, L_{short} = 5 µH, R_{short} = 100 mΩ, T_A = –40ºC	D	200 k	30	0
Hot Repetitive - Long Pulse	Terminal Short Circuit, L_{short} = 5 µH, R_{short} = 100 mΩ, T_A = 25ºC	D	100 hours	30	0

10.1.7 Thermal Information

When outputting current, the will heat up due to the power dissipation. 图 55 shows the transient thermal impedance curve that can be used to determine the device temperature during 1 W pulse of a given length.

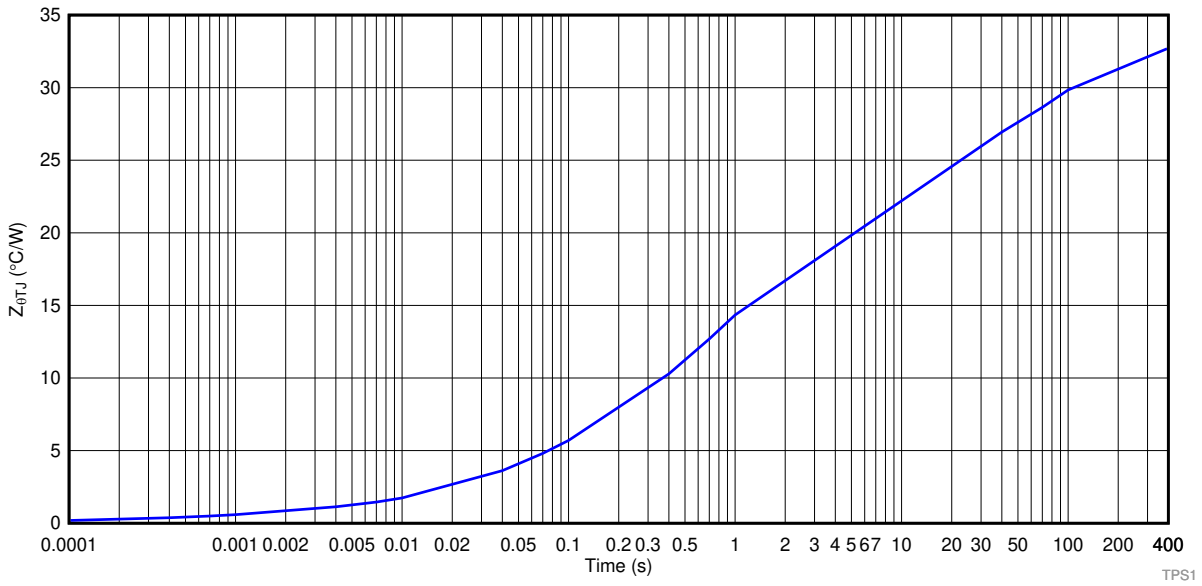


图 55. Transient Thermal Impedance

10.2 Typical Application

This application example demonstrates how the device can be used to power resistive heater loads as in seat heaters. 图 56 shows a typical application where the load is a resistive seat heater. This document highlights the basics of this type of application, however for a more detailed discussion reference *TI's Smart Power Switch Seat Heater Reference Design*.

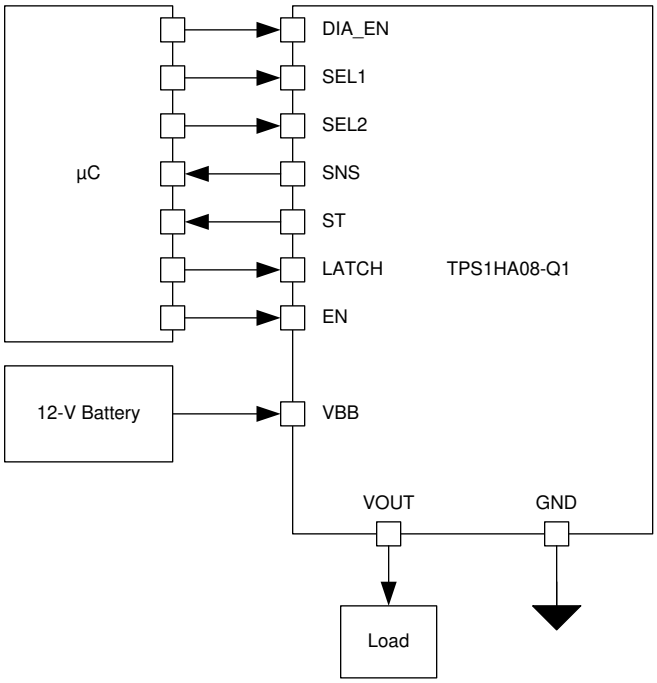


图 56. Block Diagram for Powering Heater Loads

Typical Application (接下页)

10.2.1 Design Requirements

For this design example, use the input parameters shown in 表 7.

表 7. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
V_{BB}	12.8 V
Heater Load	90 W max
Load Current Sense	100 mA to 20 A
Ambient temperature	85°C
$R_{\theta JA}$	32.8°C/W (depending on PCB)

10.2.2 Detailed Design Procedure

10.2.2.1 Thermal Considerations

The DC current under maximum load power condition will be around 7.03 A. Power dissipation in the switch is calculated in 公式 3. R_{ON} is assumed to be 20 mΩ because this is the maximum specification. In practice, R_{ON} will be lower.

$$P_{FET} = I^2 \times R_{ON} \quad (3)$$

$$P_{FET} = (7.03\ A)^2 \times 20\ m\Omega = 0.988\ W \quad (4)$$

The junction temperature of the device can be calculated using 公式 5 and the $R_{\theta JA}$ value from the *Specifications* section.

$$T_J = T_A + R_{\theta JA} \times P_{FET} \quad (5)$$

$$T_J = 85°C + 32.8°C/W \times 0.988\ W = 117.4°C$$

The maximum junction temperature rating for device is T_J = 150°C. Based on the above example calculation, the device temperature will stay below the maximum rating.

10.2.2.2 Diagnostics

If the resistive heating load is disconnected (heater malfunction), an alert is desired. Open-load detection can be performed in the switch-enabled state via the current sense feature of the device. Alternatively, under open load condition in off-state with diagnostics enabled, the current in the SNS pin will be the fault current and the can be detected from the sense voltage measurement.

10.2.2.2.1 Selecting the R_{ISNS} Value

表 8 shows the requirements for the load current sense in this application. The K_{SNS} value is specified for the device and can be found in the *Specifications* section.

表 8. R_{SNS} Calculation Parameters

PARAMETER	EXAMPLE VALUE
Current Sense Ratio (K_{SNS})	4600
Largest diagnosable load current	20 A
Smallest diagnosable load current	50 mA
Full-scale ADC voltage	5 V
ADC resolution	10 bit

The load current measurement requirements of 20 A ensures that current can be sensed up to the 20 A current limit, while the low level of 100 mA allows for accurate measurement of low load currents.

The R_{SNS} resistor value should be selected such that the largest diagnosable load current puts V_{SNS} at about 90% of the ADC full-scale. With this design, any ADC value above 90% can be considered a fault. Additionally, the R_{SNS} resistor value should ensure that the smallest diagnosable load current does not cause V_{SNS} to fall below 1 LSB of the ADC. With the given example values, a 1-kΩ sense resistor satisfies both requirements shown in 表 9.

表 9. V_{SNS} Calculation

LOAD (A)	SENSE RATIO	I_{SNS} (mA)	R_{SNS} (Ω)	V_{SNS} (V)	% OF 5-V ADC
0.050	4600	0.011	1000	0.011	0.22%
20.000	4600	4.348	1000	4.348	87%

10.2.3 Application Curves

图 57 shows the behavior of the in this application when the MCU provides an enable pulse to beginning heating the resistive element. Shortly after the EN pin goes high, the load current begins to flow and the SNS pin measures the output current.

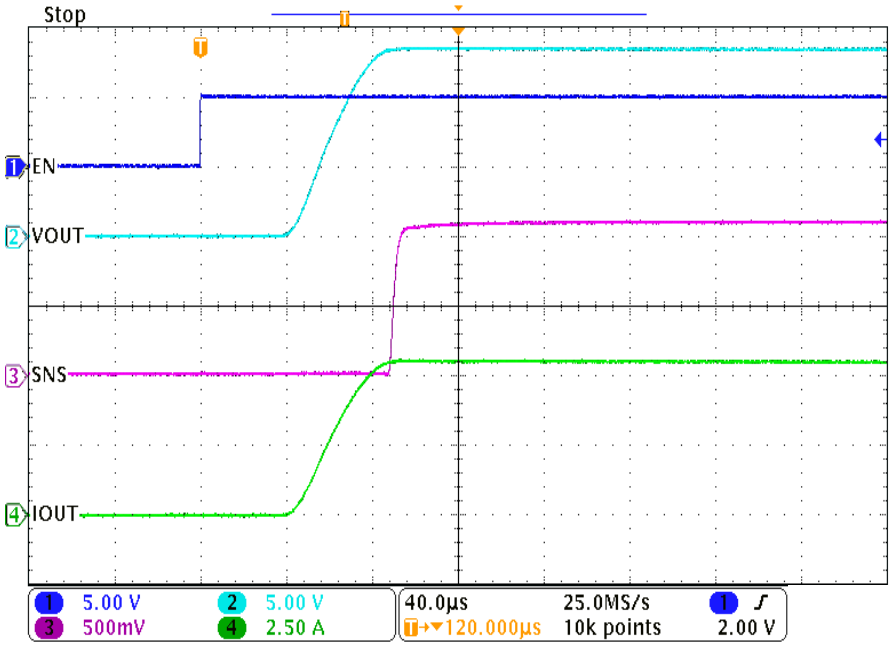


图 57. Heater Turn-on Time

By measuring the voltage on the SNS pin, the can communicate back to the system MCU what the load current is. 图 58 shows that when the seat heater approaches full load and I_{OUT} jumps from a low load current of 1 A up to a 5 A load current, the load step is mirrored on the SNS pin.

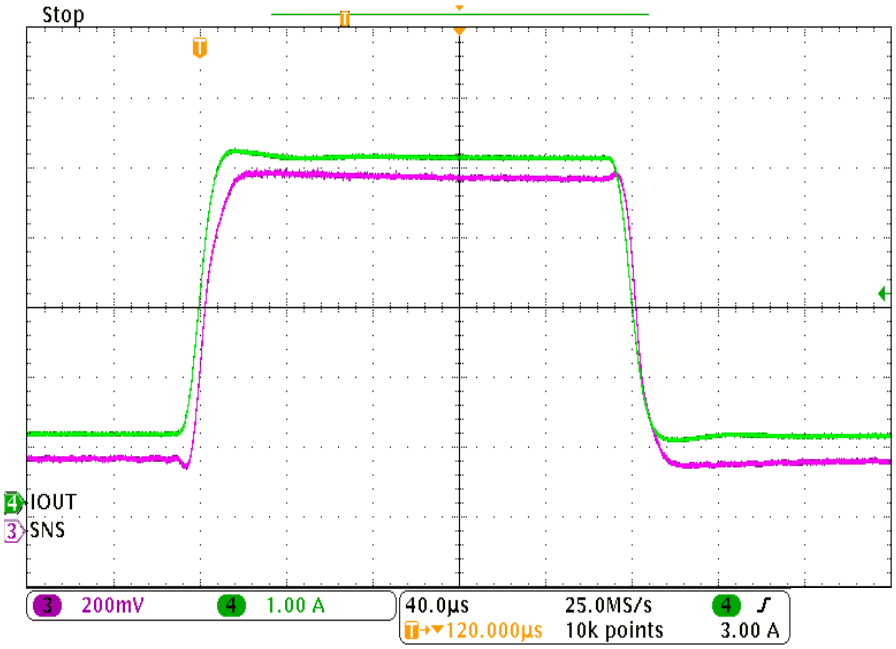


图 58. SNS Response During Heater Load Step

One common concern in these type of applications is that the heating element can accidentally lose connection, creating an open load situation. In this case, it is ideal for the to recognize that the load has been removed and report a FLT to the MCU. 图 59 shows the behavior of the when there is no load attached. As soon as the DIAG_EN pin is engaged, the SNS output goes high and the $\overline{ST}$ output engages low. By monitoring these pins, the MCU can recognize there is a fault and notify the user that maintenance is required.

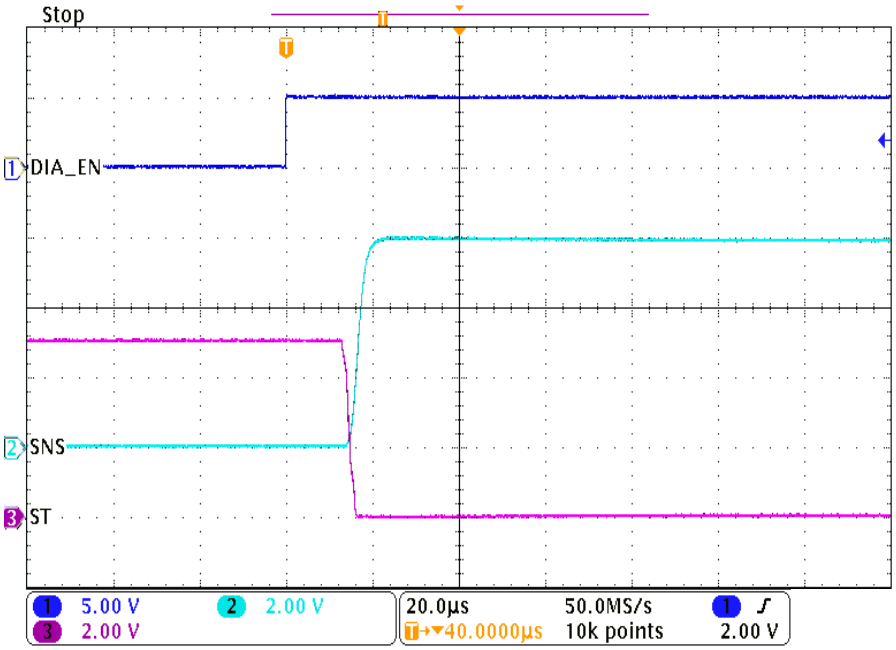


图 59. Open Load Detection If Heating Element is Missing

Importantly, the will also protect the system in the event of a short-circuit. 图 60 shows the behavior of the device if it is enabled into a short circuit condition. If this is using the device option C, the current will be clamped to the current limit I_{CL} until it hits an over temperature event, at which point it will shut down. In this way, the system is protected from unchecked overcurrent in the event of a short circuit.

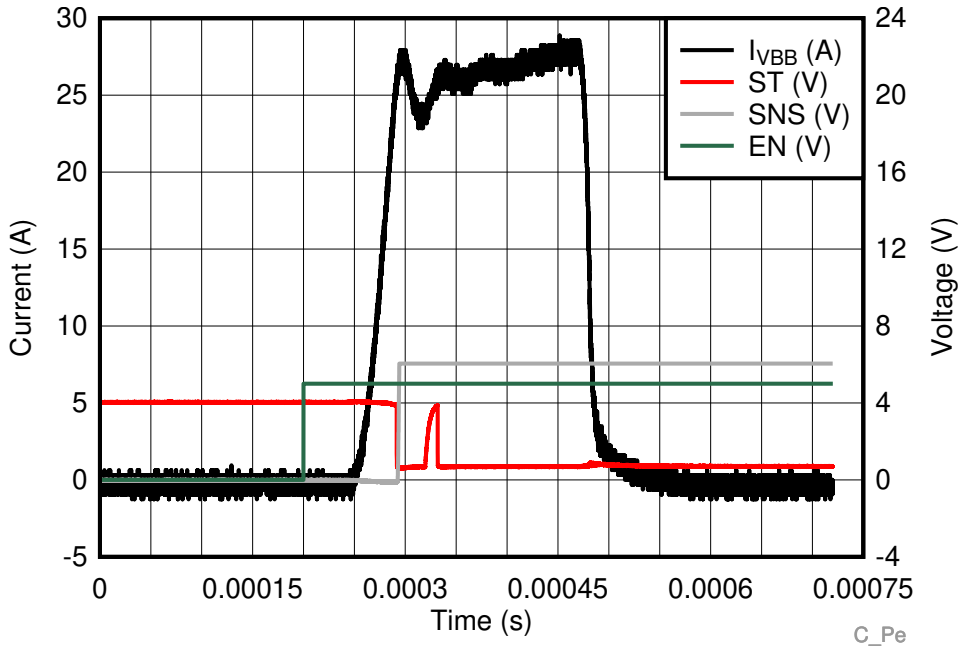


图 60. Overcurrent Behavior During Short Circuit Event

11 Power Supply Recommendations

The is designed to operate in a 12-V automotive system. The nominal supply voltage range is 8 V to 18 V. The device is also designed to withstand voltage transients beyond this range. When operating outside of the nominal voltage range, the device will exhibit normal functional behavior. However, parametric specifications may not be guaranteed.

表 10. Operating Voltage Range

V_{BB} Voltage Range	Note
3 V to 8 V	Transients such as cold crank and start-stop, functional operation guaranteed but some parametric specifications may not apply. The device is completely short-circuit protected up to 125°C
8 V to 18 V	Nominal supply voltage, all parametric specifications apply. The device is completely short-circuit protected up to 125°C
18 V to 40 V	Transients such as jump-start and load-dump, functional operation guaranteed but some parametric specifications may not apply

12 Layout

12.1 Layout Guidelines

To achieve optimal thermal performance, connect the exposed pad to a large copper pour. On the top PCB layer, the pour may extend beyond the pad dimensions as shown in the example below. In addition to this, it is recommended to also have a V_{BB} plane either on one of the internal PCB layers or on the bottom layer. Vias should connect this plane to the top V_{BB} pour.

has 6 V_{OUT} pins. All V_{OUT} pins must be shorted together on the PCB. Additionally, the layout should ensure that the current path is symmetrical for both sides of the device. If the path is not symmetrical, there will be some imbalance in current spreading across the power FET. This can impact accuracy of the current sense measurement.

12.2 Layout Example

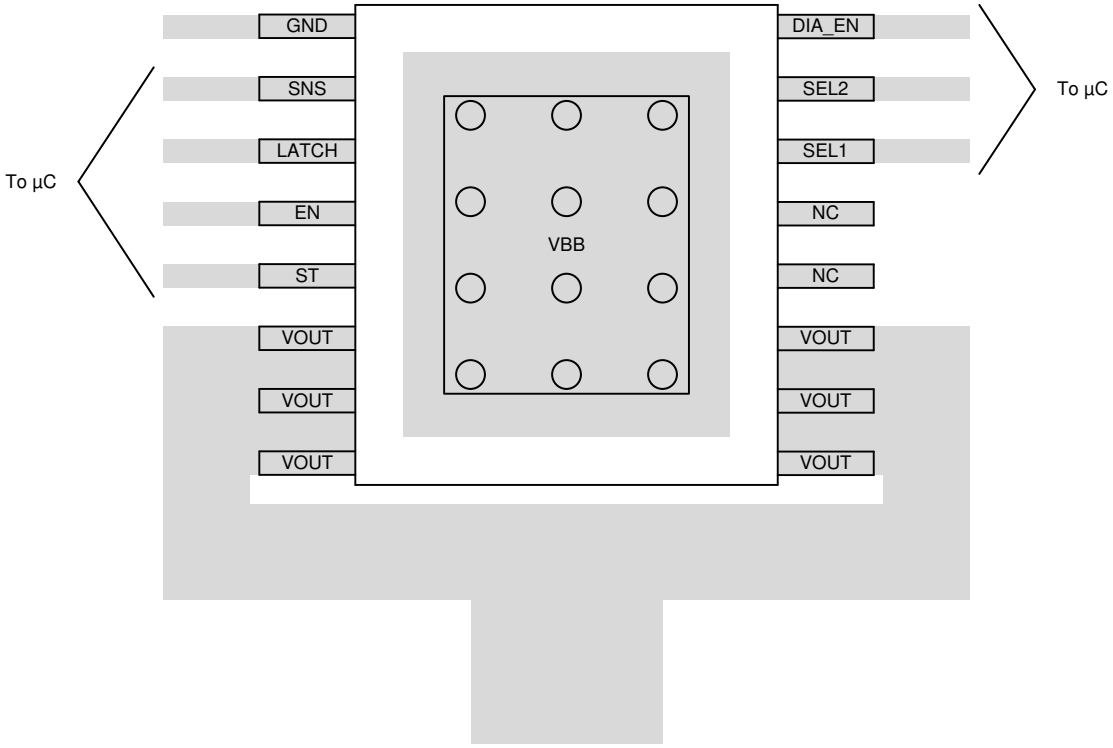


图 61. PWP Layout Example

13 器件和文档支持

13.1 器件支持

13.1.1 相关文档

请参阅如下相关文档：

- *TI《如何利用智能高侧开关驱动电感、电容和照明负载》*
- *《智能电源开关的短路可靠性测试》*
- *TI《智能电源开关座椅加热器参考设计》*
- *适用于高侧开关的反向电池保护*

13.2 商标

All trademarks are the property of their respective owners.

13.3 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

13.4 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

14 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS1HA08AQPWPRQ1	ACTIVE	HTSSOP	PWP	16	3000	RoHS-Exempt & Green	NIPDAU	Level-3-260C-168HRS	-40 to 125	1HA08A	Samples
TPS1HA08BQPWPRQ1	ACTIVE	HTSSOP	PWP	16	3000	RoHS-Exempt & Green	NIPDAU	Level-3-260C-168HRS	-40 to 125	1HA08B	Samples
TPS1HA08CQPWPRQ1	ACTIVE	HTSSOP	PWP	16	3000	RoHS-Exempt & Green	NIPDAU	Level-3-260C-168HRS	-40 to 125	1HA08C	Samples
TPS1HA08DQPWPRQ1	ACTIVE	HTSSOP	PWP	16	3000	RoHS-Exempt & Green	NIPDAU	Level-3-260C-168HRS	-40 to 125	1HA08D	Samples
TPS1HA08EQPWPRQ1	ACTIVE	HTSSOP	PWP	16	3000	RoHS-Exempt & Green	NIPDAU	Level-3-260C-168HRS	-40 to 125	1HA08E	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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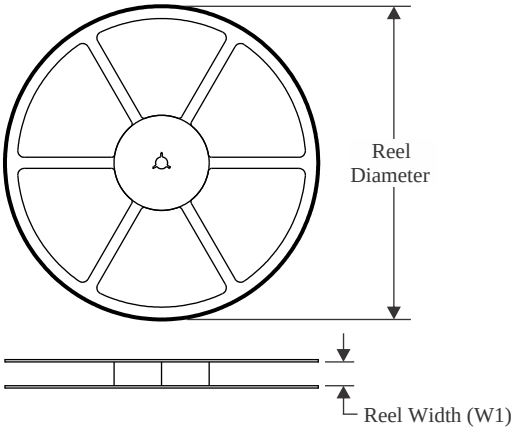
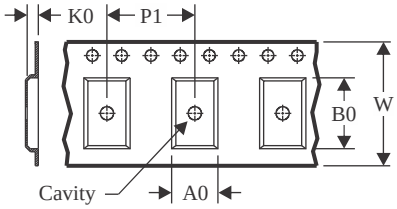
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

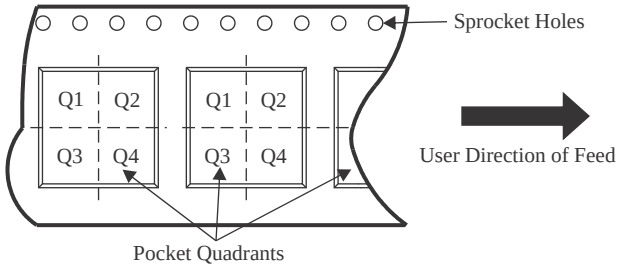


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

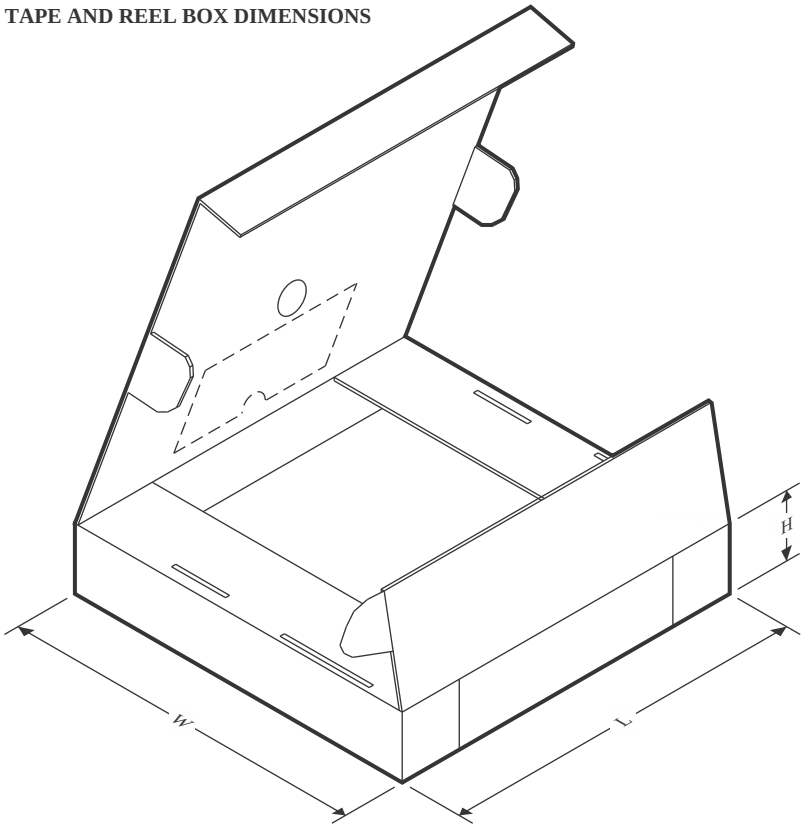
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS1HA08AQPWPRQ1	HTSSOP	PWP	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TPS1HA08BQPWPRQ1	HTSSOP	PWP	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TPS1HA08CQPWPRQ1	HTSSOP	PWP	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TPS1HA08DQPWPRQ1	HTSSOP	PWP	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TPS1HA08EQPWPRQ1	HTSSOP	PWP	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

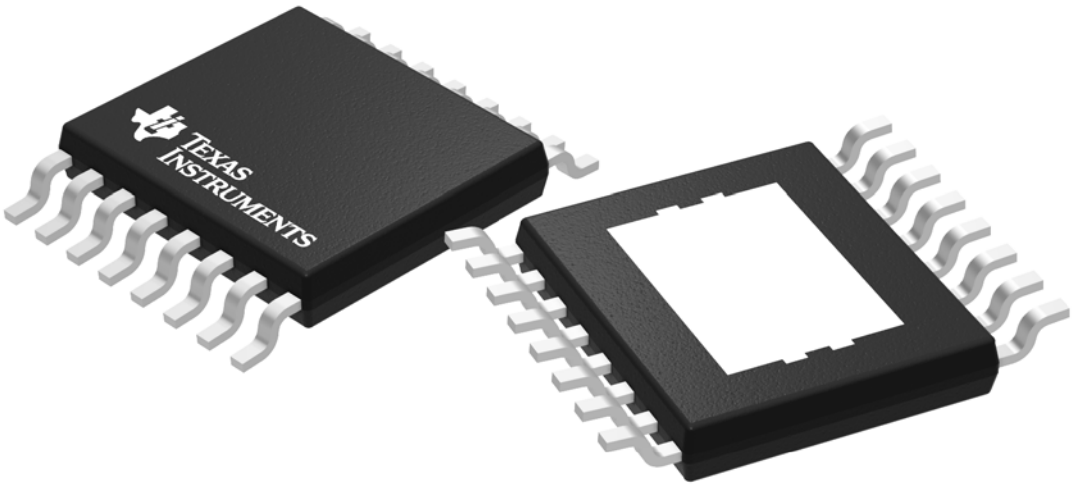


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS1HA08AQPWPRQ1	HTSSOP	PWP	16	3000	350.0	350.0	43.0
TPS1HA08BQPWPRQ1	HTSSOP	PWP	16	3000	350.0	350.0	43.0
TPS1HA08CQPWPRQ1	HTSSOP	PWP	16	3000	350.0	350.0	43.0
TPS1HA08DQPWPRQ1	HTSSOP	PWP	16	3000	350.0	350.0	43.0
TPS1HA08EQPWPRQ1	HTSSOP	PWP	16	3000	350.0	350.0	43.0

PWP 16 PowerPAD™ TSSOP - 1.2 mm max height

PLASTIC SMALL OUTLINE



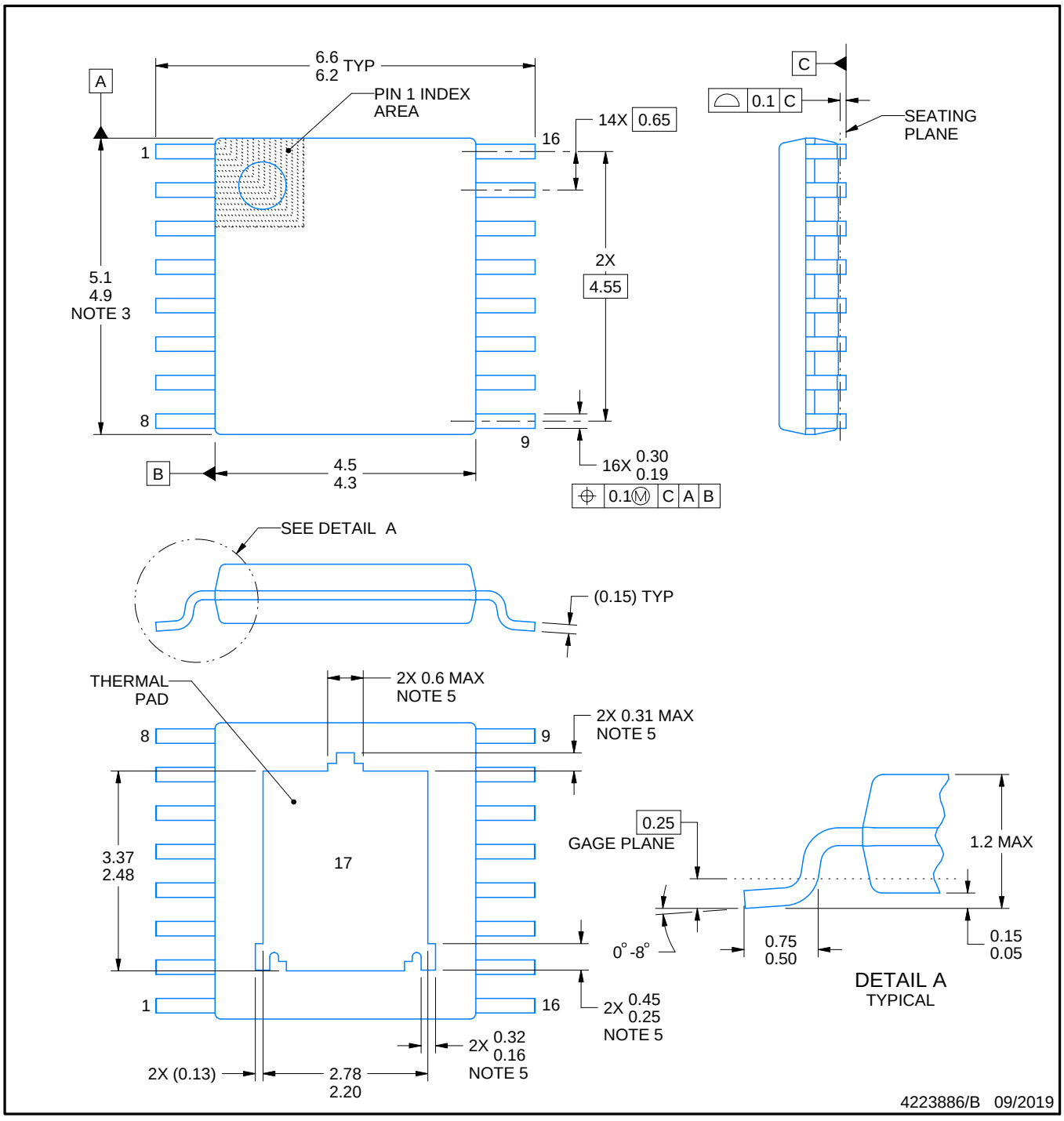
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

PACKAGE OUTLINE

PWP0016M

PowerPAD™ TSSOP - 1.2 mm max height

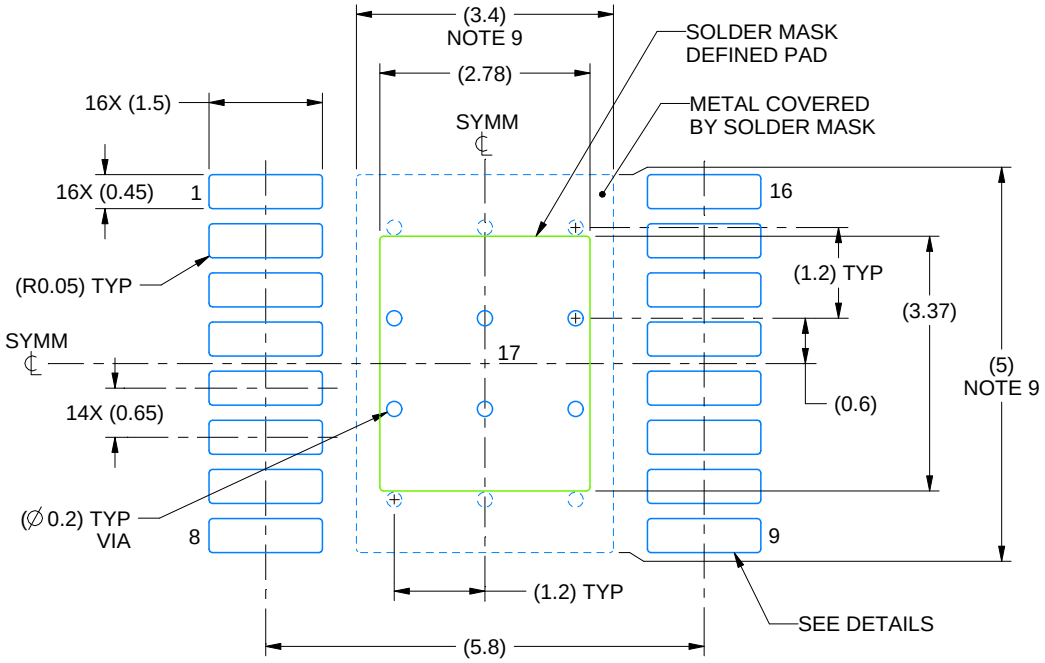
SMALL OUTLINE PACKAGE



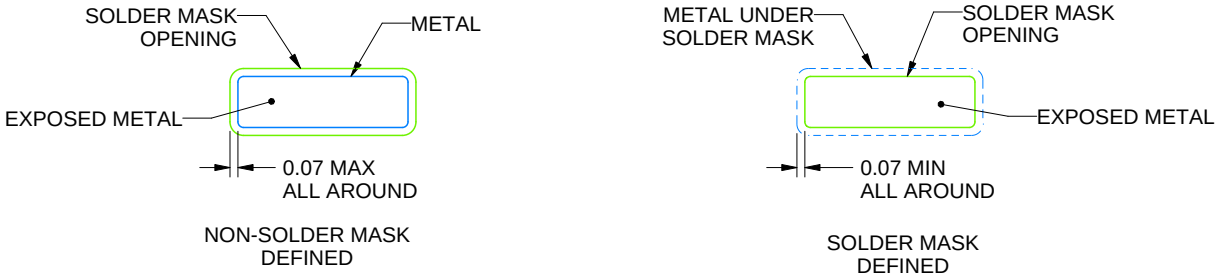
PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-153.
5. Features may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

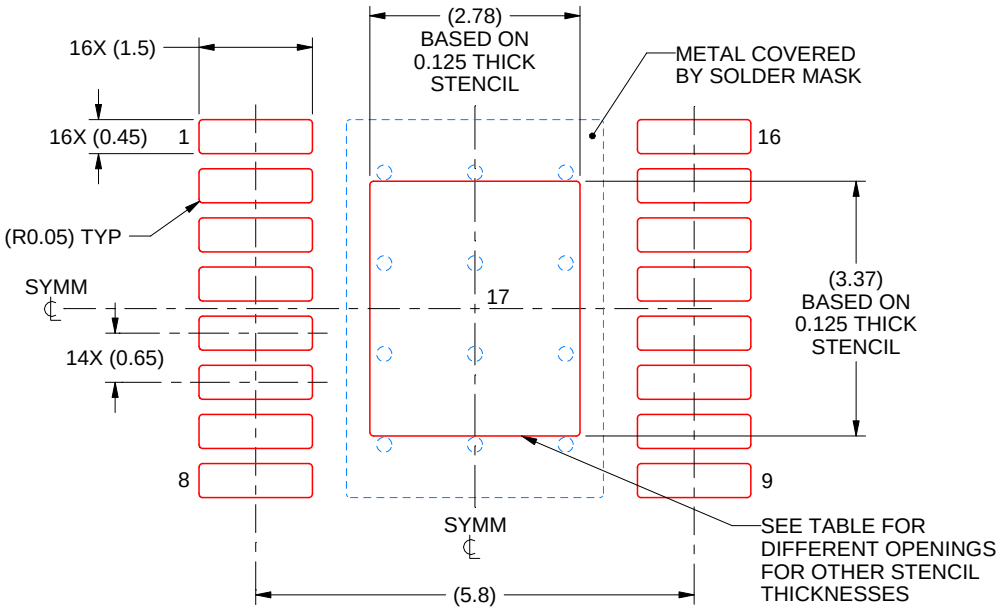


SOLDER MASK DETAILS

4223886/B 09/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
9. Size of metal pad may vary due to creepage requirement.
10. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	3.11 X 3.77
0.125	2.78 X 3.37 (SHOWN)
0.15	2.54 X 3.08
0.175	2.35 X 2.85

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NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

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